STE2000

65 X 128 SINGLE CHIP LCD CONTROLLER / DRIVER

PRODUCT PREVIEW

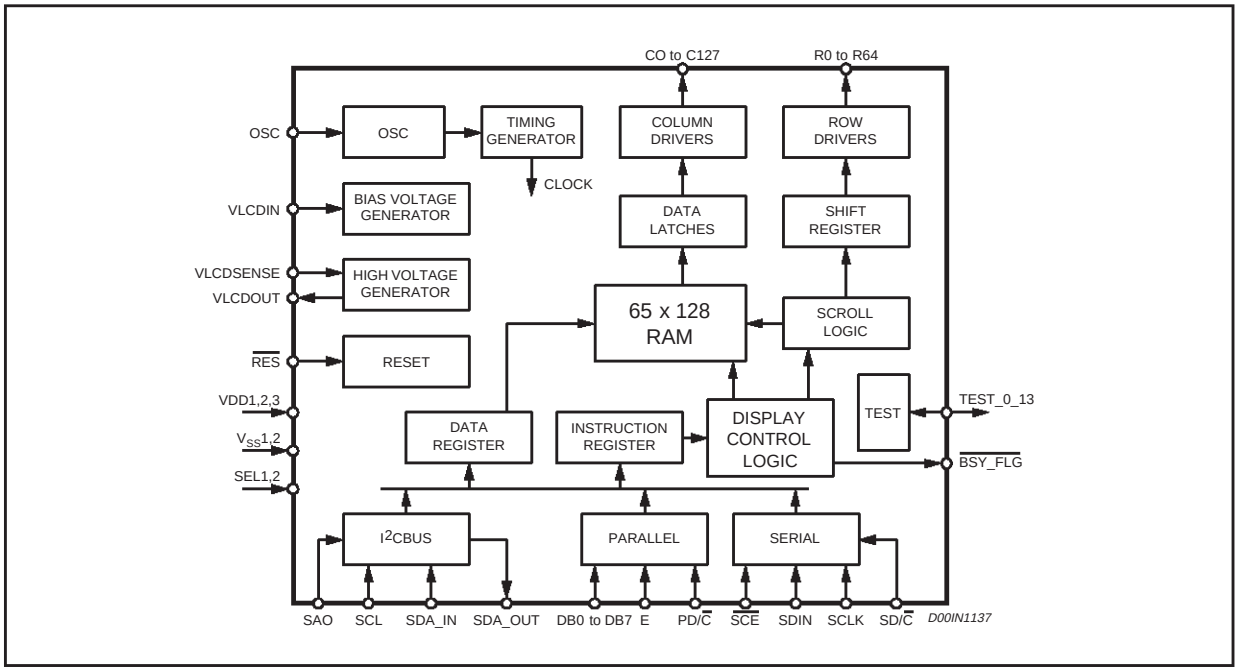
- 65 x 128 bits Display Data RAM
- Configurable matrix: 65 x 128 or 33 x 160
- Programmable (65/33) MUX rate
- Row by Row Scrolling
- Automatic data RAM Blanking procedure
- Selectable Input Interface:
  - I^2C Bus Fast and Hs-mode (read and write)
  - Parallel Interface (write only)
  - Serial Interface (write only)
- Fully Integrated Oscillator requires no external components
- CMOS Compatible Inputs (5V tolerant)
- Fully Integrated Configurable LCD bias voltages generator with:
  - Selectable (5X, 4X, 3X, 2X) multiplication factor
  - Effective sensing for High Precision Output
  - Four selectable temperature compensation coefficients
- Designed for chip-on-glass (COG) applications
- Programmable bottom row pads mirroring and top row pads mirroring for compatible with both TCP and COG applications
- Low Power Consumption, suitable for battery operated systems
- Logic Supply Voltage range from 1.9 to 5.5V
- High Voltage Generator Supply Voltage range from 2.4 to 4.5V
- Display Supply Voltage range from 4.5 to 9V

DESCRIPTION

The STE2000 is a low power CMOS LCD controller driver. Designed to drive a 65 rows by 128 columns graphic display, provides all necessary functions in a single chip, including on-chip LCD supply and bias voltages generators, resulting in a minimum of externals components and in a very low power consumption. The STE2000 features three standard interfaces (Serial, parallel, I^2C) for ease of interfacing with the host µcontroller.

Type	Ordering Number
Bumped Wafers	
Bumped Dice on Waffle Pack	

Figure 1. Block Diagram



PIN DESCRIPTION

N°	Pad	Type	Function
R0 to R64	1 to 16 145 to 176 256 to 272	O	LCD Row Driver Output
C0 to C127	17 to 144	O	LCD Column Driver Output
$V_{SS1,2}$	195 to 206	GND	Ground pads. V_{SS1} is GND for V_{DD1}, V_{SS2} for V_{DD2} and V_{DD3}
V_{DD1}	242 to 247	Supply	IC Positive Power Supply
$V_{DD2,3}$	232 to 241	Supply	Internal Generator Supply Voltages.
V_{LCDIN}	182 to 187	Supply	LCD Supply Voltages for the Column and Row Output Drivers.
V_{LCDOUT}	189 to 194	Supply	Voltage Multiplier Output
$V_{LCDSENSE}$	188	Supply	Voltage Multiplier Regulation Input. V_{LCDOUT} Sensing for Output Voltage Fine Tuning
SEL1,2	249, 250	I	Interface Mode Selection
SDA_IN	210	I	I^2C Bus Data In
SDA_OUT	211	O	I^2C Bus Data Out
SCL	209	I	I^2C bus Clock
SA0	208	I	I^2C Slave Address LSB
OSC	248	I	External Oscillator Input
$\overline{RES}$	212	I	Reset Input. Active Low.
DB0 to DB7	215 to 222	I	Parallel Interface 8 Bit Data Bus
E	213	I	Parallel Interface Data Latch Signal. Data are Latched on the Falling EDGE.
PD/$\overline{C}$	214	I	Parallel Interface Data/Command Selector
SDIN	226	I	Serial Interface Data Input
SCLK	223	I	Serial Interface Clock
$\overline{SCE}$	224	I	Serial Interface ENABLE. When Low the Incoming Data are Clocked In.
SD/$\overline{C}$	225	I	Serial Interface Data/Command selection
$\overline{BSYFLG}$	227	O	Active Procedure Flag. Notice if There is an ongoing Internal Operation. Active Low.
T1 to T13	177 to 181 228 to 231 251 to 255	I/O	Test Pads.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD1}	Supply Voltage Range	- 0.5 to + 6.5	V
$V_{DD2,3}$	Supply Voltage Range	- 0.5 to + 5	V
V_{LCD}	LCD Supply Voltage Range	- 0.5 to + 10	V
I_{SS}	Supply Current	- 50 to +50	mA
V_i	Input Voltage (all input pads)	-0.5 to V_{DD} + 0.5	V
I_{in}	DC Input Current	- 10 to + 10	mA
I_{out}	DC Output Current	- 10 to + 10	mA
P_{tot}	Total Power Dissipation (T_j = 85°C)	300	mW
P_o	Power Dissipation per Output	30	mW
T_j	Operating Junction Temperature	-40 to + 85	°C
T_{stg}	Storage Temperature	- 65 to 150	°C

ELECTRICAL CHARACTERISTICS

DC OPERATION

(V_{DD1} = 1.9 to 5.5V; $V_{DD2,3}$ = 2.4 to 4.5 V; $V_{ss1,2}$ = 0V; V_{LCD} = 4.5 to 9V; T_{amb} =-40 to 85°C; unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Supply Voltages						
V_{DD1}	Supply Voltage		1.9		5.5	V
		T_{amb} =-20 to 85°C	1.8		5.5	V
$V_{DD2,3}$	Supply Voltage	LCD Voltage Internally generated	2.4		4.5	V
V_{LCDIN}	LCD Supply Voltage	LCD Voltage Supplied externally	4.5		9	V
V_{LCDOUT}	LCD Supply Voltage	Internally generated; note 1	4.5		9	V
$I(V_{DD1})$	Supply Current	V_{DD} = 2.8V; V_{LCD} = 7.6V; 4x charge pump; f_{sclk} = 0; T_{amb} = 25°C; note 3.		20		µA
$I(V_{DD2,3})$	Voltage Generator Supply Current	with VOP = 0 and PRS = 0 with external V_{LCD}		0.5		µA
		V_{LCD} =7.6V; f_{sclk} = 0; T_{amb} = 25°C; no display load; 4x charge pump; note 2,3,6		200		µA
$I(V_{DD1,2,3})$	Total Supply Current	V_{LCD} = 7.6V;4x charge pump; f_{sclk} = 0; T_{amb} = 25°C; no display load; note 2,3,6		220	350	µA
$I(V_{LDCIN})$	External LCD Supply Voltage Current	V_{DD} =2.8V; V_{LCD} =7.6V;no display load; f_{sclk} = 0; T_{amb} = 25°C; note 3.		30		µA

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Logic Inputs						
V_{IL}	Logic LOW voltage level		V_{SS}		0.3 V_{DD}	V
V_{IH}	Logic HIGH Voltage Level		0.7 V_{DD}		5.5	V
I_{in}	Input Current	V_{in} = V_{SS1} or V_{DD1}	-1		1	µA
Column and Row Driver						
R_{row}	ROW Output Resistance	V_{IN} = V_{ih} (t_p < 10µs)		12	20	kohm
R_{col}	Column Output resistance	V_{IN} = V_{il} (t_p < 10µs)		12	20	kohm
V_{col}	Column Bias voltage accuracy	No load	-100		100	mV
V_{row}	Row Bias voltage accuracy		-100		100	mV
LCD Supply Voltage						
V_{LCD}	LCD Supply Voltage accuracy; Internally generated	V_{DD} = 2.8V; V_{LCD} = 7.6V; fsclk=0; Tamb=25 C; no display load; note 2, 3, 6 & 7	-300		300	mV
TC	Temperature coefficient	00		$-0.0 \cdot 10^{-3}$		1/°C
		01		$-0.76 \cdot 10^{-3}$		1/°C
		10		$-1.05 \cdot 10^{-3}$		1/°C
		11		$-2.10 \cdot 10^{-3}$		1/°C

Notes: 1. The maximum possible V_{LCD} voltage that can be generated is dependent on voltage, temperature and (display) load.
2. Internal clock
3. When f_{sclk} = 0 there is no interface clock.
4. Power-down mode. During power-down all static currents are switched-off.
5. If external V_{LCD}, the display load current is not transmitted to I_{DD}
6. Tolerance depends on the temperature; (typically zero at T_{amb} = 27°C), maximum tolerance values are measured at the temperature range limit.
7. For TC0 to TC3

AC OPERATION

(V_{DD1} = 1.9 to 5.5V; $V_{DD2,3}$ = 2.4 to 4.5 V; $V_{ss1,2}$ = 0V; V_{LCD} = 4.5 to 9V; T_{amb} =-40 to 85°C; unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
INTERNAL OSCILLATOR						
F_{OSC}	Internal Oscillator frequency	V_{DD} = 2.8V; T_{amb} = -20 to +70 °C	20	38	70	kHz
F_{EXT}	External Oscillator frequency		20	38	100	kHz
F_{FRAME}	Frame frequency	fosc or fext = 38 kHz; note 1		73		Hz
T_{VHRL}	Vdd1 to $\overline{RES}$ Low	note 2 and 10; C_{VLCD} = 1µF	0		5	ms

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$T_{w(RES)}$	$\overline{RES}$ LOW pulse width	note 3	450			ns
I²C BUS INTERFACE (See note 4)						
F_{SCL}	SCL Clock Frequency	Fast Mode	DC		400	kHz
		High Speed Mode; Cb=100pF (max); note 6	DC	3.4		MHz
		High Speed Mode; Cb=400pF (max); note 6	DC	1.7		MHz
T_{SCLL}	Cb=100pF		160			ns
T_{SCLH}	Cb=100pF		160			ns
T_{SCLL}	Cb=400pF		320			ns
T_{SCLH}	Cb=400pF		320			ns
$T_{SU;DAT}$	Cb=100pF			30		ns
$T_{HD;DAT}$	Cb=100pF			30		ns
$T_{SU;DAT}$	Cb=400pF			30		ns
$T_{HD;DAT}$	Cb=400pF			30		ns
$T_{SU;STA}$	Cb=100pF	Note 8	160			ns
$T_{SU;STA}$	Cb=400pF	Note 8	320			ns
$T_{HD;STA}$	Cb=100pF	Note 8	160			ns
$T_{HD;STA}$	Cb=400pF	Note 8	320			ns
$T_{SU;STO}$	Cb=100pF	Note 8	160			ns
$T_{SU;STO}$	Cb=400pF	Note 8	320			ns
T_{rCL}	Cb=100pF	Note 5, 8	10		40	ns
T_{rCL}	Cb=400pF	Note 5, 8	20		80	ns
T_{rCL1}	Cb=100pF	Note 5, 8	20		40	ns
T_{rCL1}	Cb=400pF	Note 5, 8	80		160	ns
T_{rDA}	Cb=100pF	Note 5, 8	20		40	ns
T_{rDA}	Cb=400pF	Note 5, 8	80		160	ns
T_{fCL}	Cb=100pF	Note 5, 8	10		40	ns
T_{fCL}	Cb=400pF	Note 5, 8	20		80	ns
T_{fDA}	Cb=100pF		10		40	ns
T_{fDA}	Cb=400pF		80		160	ns

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_b	Capacitive load for SDAH and SCLH		100		400	pF
C_b	Capacitive load for SDAH + SDA line and SCLH + SCL line				400	pF
T_{SW}		note 5		10		ns
PARALLEL INTERFACE						
$T_{CY(EN)}$	Enable Cycle Time	V_{DD} = 4.5V; Write	125			ns
$T_{W(EN)}$	Enable Pulse width	V_{DD} = 4.5V; Write	60			ns
$T_{SU(A)}$	Address Set-up Time	V_{DD} = 4.5V; Write	20			ns
$T_{H(A)}$	Address Hold Time	V_{DD} = 4.5V; Write	40			ns
$T_{SU(D)}$	Data Set-Up Time	V_{DD} = 4.5V; Write	20			ns
$T_{H(D)}$	Data Hold Time	V_{DD} = 4.5V; Write	40			ns
SERIAL INTERFACE						
F_{SCLK}	Clock Frequency	V_{DD} = 4.5V		8		MHz
T_{CYC}	Clock Cycle SCLK	V_{DD} = 4.5V	125			ns
T_{PWH1}	SCLK pulse width HIGH	V_{DD} = 4.5V	60			ns
T_{PWL1}	SCLK Pulse width LOW	V_{DD} = 4.5V	60			ns
T_{S2}	$\overline{SCE}$ setup time		40			ns
T_{H2}	$\overline{SCE}$ hold time		40			ns
T_{PWH2}	$\overline{SCE}$ minimum high time		50			ns
T_{H5}	$\overline{SCE}$ start hold time	Note 8	50			ns
T_{S3}	SD/$\overline{C}$ setup time		30			ns
T_{H3}	SD/$\overline{C}$ hold time		30			ns
T_{S4}	SDIN setup time		30			ns
T_{H4}	SDIN hold time		30			ns

Notes: 1. $F_{frame} = \frac{f_{osc}}{520}$

2. $\overline{RES}$ may be LOW or HIGH before V_{DD1} goes HIGH.
3. If $T_{w(RES)}$ is longer than 500ns (typical) a reset may be generated.
4. All timing values are valid within the operating supply voltage and ambient temperature ranges and referenced to V_{IL} and V_{IH} with an input voltage swing of V_{SS} to V_{DD}
5. The rise and fall times specified here refer to the driver device and are part of general Hs-mode specification.
6. The device inputs SDA and SCL are filtered and will reject any spike on the bus-lines of with T_{SW}
7. Cb is the capacitive load for each bus line.
8. T_{H5} is the time from the previous SCLK positive edge to the negative edge of $\overline{SCE}$
9. For bus line loads Cb between 100 and 400pF the timing parameters must be linearly interpolated
10. C_{VLCD} is the filtering capacitor on VLCDOUT

CIRCUIT DESCRIPTION

Supplies Voltages and Grounds

V_{DD2} and V_{DD3} are supply voltages to the internal voltage generator (see below). They must be externally connected. If the internal voltage generator is not used, these should be connected to V_{DD1} pad. V_{DD1} supplies the rest of the IC. This supply voltage could be different form V_{DD2} and V_{DD3}.

Internal Supply Voltage Generator

The IC has a fully integrated (no external capacitors required) charge pump for the Liquid Crystal Display supply voltage generation. The multiplying factor can be programmed to be: X5; X4; X3; X2, using the 'set CP Multiplication' Command. The output voltage (V_{LCDOUT}) is tightly controlled through the $V_{LCDSENSE}$ pad. For this voltage, four different temperature coefficients (TC, rate of change with temperature) can be programmed using the bits TC1 and TC0. This will ensure no contrast degradation over the LCD operating range. Using the internal charge pump, the V_{LCDIN} and V_{LCDOUT} pads must be connected together. An external supply could be connected to V_{LCDIN} to supply the LCD without using the internal generator. In such event the V_{LDCOUT} and $V_{LCDSENSE}$ must be connected to GND and the internal voltage generator must be programmed to zero (PRS = 0, Vop = 0 - Reset condition).

Oscillator

A fully integrated oscillator (requires no external components) is present to provide the clock for the Display System. When used the OSC pad must be connected to VDD1 pad. An external oscillator could be used and fed into the OSC pin.

Display Data RAM

The STE2000, provides an 65X128 bits Static RAM to store Display data. This is organized into 8 (Bank0 to Bank7) banks with 128 Bytes and one Bank (Bank8) with 128 Bits to be used for icons. RAM access is accomplished in either one of the Bus Interfaces provided (see below). Allowed addresses are X0 to X127 (Horizontal) and Y0 to Y8 (Vertical).

When writing to RAM, four addressing mode are provided:

- Normal Horizontal (MX=0 and V=0), having the column with address X= 0 located on the left of the memory map. The X pointer is increased after each byte written. After the last row address (Y=8), Y address pointer is increased to jump to next row after the last column address (X=127). X restarts from X=0 (Fig. 2)
- Normal Vertical (MX=0 and V=1), having the column with address X= 0 located on the left of the memory map. The Y pointer is increased after each byte written. X address pointer is increased to jump to next column and Y restarting from Y=0 (Fig. 3).
- Mirrored Horizontal (MX=1 and V=0), having the column with address X= 0 located on the right of the memory map. The X pointer is increased after each byte written. Y address pointer is increased to jump to next row after the last column address (X=127) and X restarting from X=0 (fig. 4).
- Mirrored Vertical (MX=1 and V=1), having the column with address X= 0 located on the right of the memory map. The Y pointer is increased after each byte written. After the last row address (Y=8), the X pointer is increased to jump to next column and Y restarting from Y=0.

After the last allowed address (X;Y)=(128;8), the address pointers always jump to the cell with address (X;Y) = (0;0).
Data bytes in the memory could have the MSB either on top (D0 = 0, Fig. 6) or on the bottom (D0=1, Fig. 7).

Mux 65 Mode

The STE2000 provides also means to alter the normal output addressing. A mirroring of the Display along the X axis is enabled setting to a logic one the MY bit. This function is achieved reading the matrix from physical row 63 to 0, since the relation between the physical memory rows and the output row drivers is only dependent on the memory reading sequence (1st row read output on R0, 2nd on R1... last on R65). This function doesn't affect the content of the memory map. It is only related to the visualization process (Fig. 8 & Fig. 9).
A flip along the local Y axis, in the order of the rows of the memory are connected to the Pads of the Device, can be also performed. This can be applied on both the Row Pads located on the Interface Side (the edge of the chip where the Interface Pads are located), setting the TRS bit to a logic one, and on the Row Pads located on the other edge, setting the BRS bit to a logic one.
Figure 2 Automatic data RAM writing sequence with V=0 and Data RAM Normal Format (MX=0) Figure 3 Automatic data RAM writing sequence with V=1 and Data RAM Normal Format (MX=0)

Figure 2. Automatic data RAM writing sequence with V=0 and Data RAM Normal Format (MX=0)

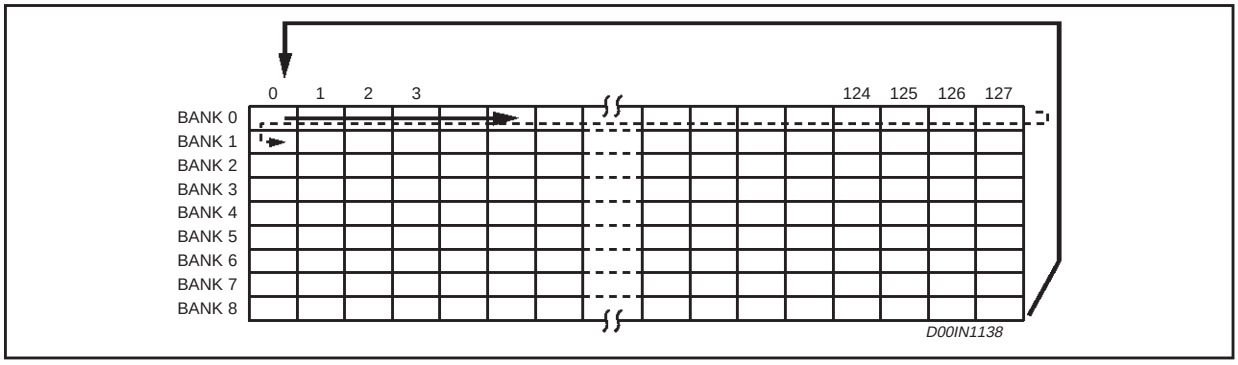


Figure 3. Automatic data RAM writing sequence with V=1 and Data RAM Normal Format (MX=0)

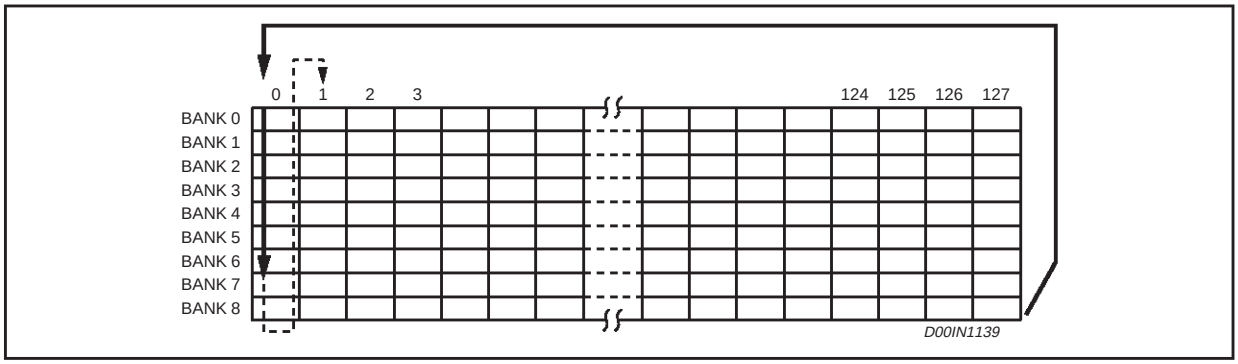


Figure 4. Automatic data RAM writing sequence with V=0 and Data RAM Mirrored Format (MX=1)

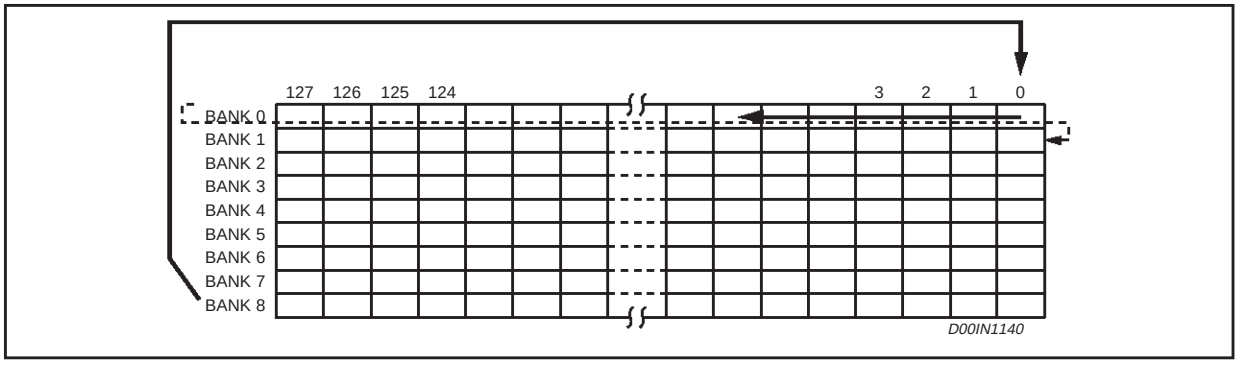


Figure 5. Automatic data RAM writing sequence with V=1 and Data RAM Mirrored Format (MX=1)

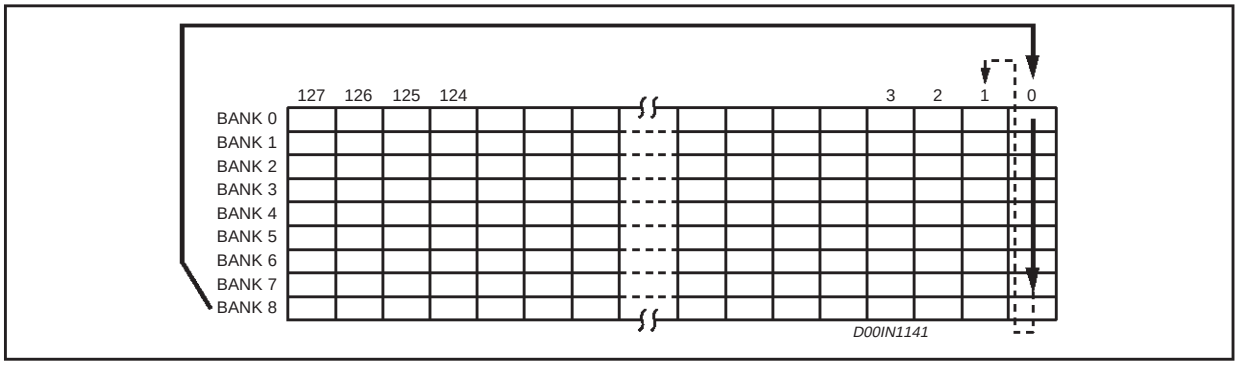


Figure 6. Data RAM Byte organization with D0 = 0

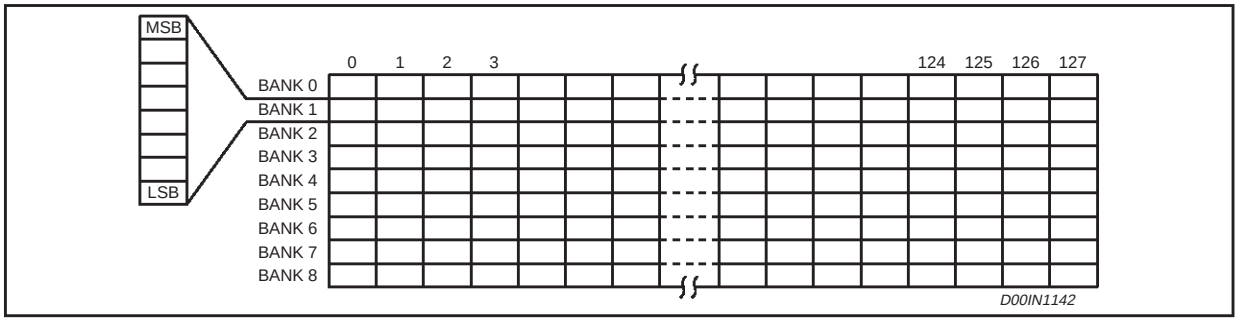


Figure 7. Data RAM Byte organization with D0 = 1

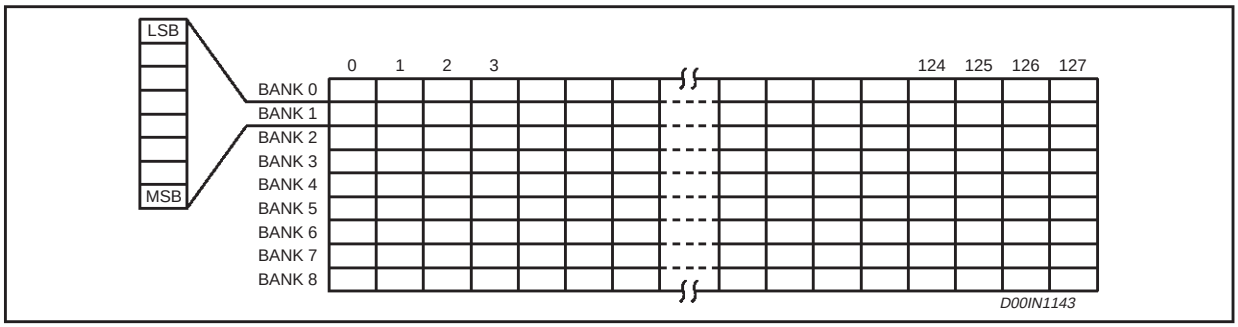


Figure 8. Output drivers rows and physical memory rows correspondence with MY =0

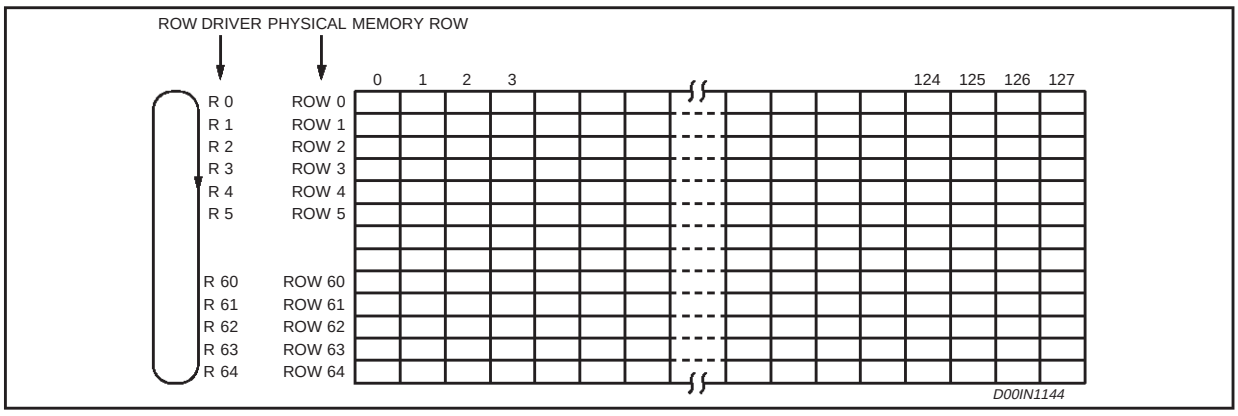
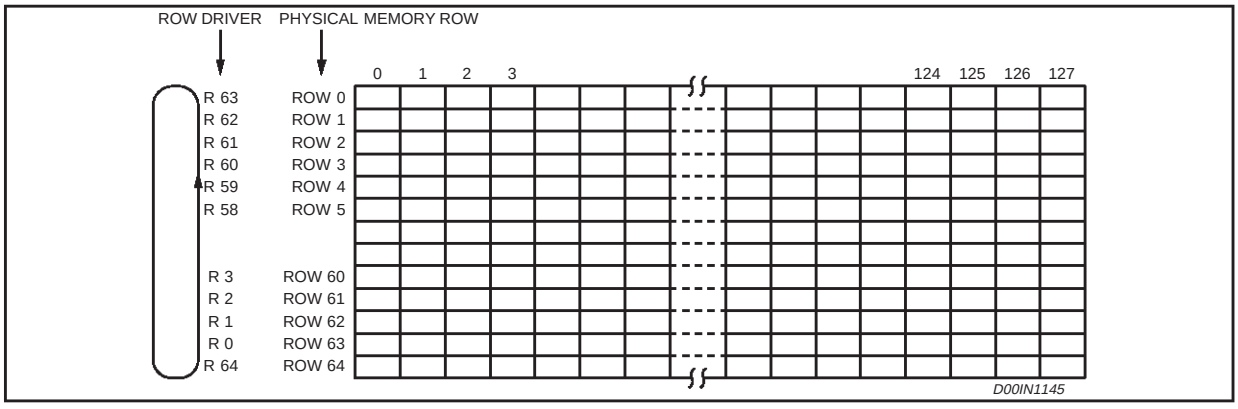


Figure 9. Output drivers rows and physical memory rows correspondence with MY =1



MUX 33 Mode

When using the 1:33 MUX ratio (MUX bit Set), the memory map is changed so that the only ”active” row drivers are the ones related to Bank4 to Bank7. These will be ”enlarged” with columns from 0 to 15 and columns from 112 to 127 coming from memory Banks 0 to 3 (Fig. 10).

To understand how the memory is affected, consider a rigid translation where Memory sector with coordinates (0;0) will still be (0;0) and (3; 15) become (7;15). Memory sector (112;0) will become (4;128) and (3;127) becoming (7;128) (see figure 10). The Icon row (Bank8) has only columns 16 to 144 valid, therefore (0;15) and (145;160) aren’t to be used. The new memory matrix is equivalent to a 33x160 matrix from the visualization point of view and a subset of the 65x128 physical memory matrix for writing purpose. When writing data RAM, as for Mux 65, four addressing mode are provided. The memory matrix is written as in mux 65 mode so the user must take care of updating the X and Y pointers to fill the memory matrix in the correct way, taking into account which banks are displayed and where are displayed

In MUX 33 mode only the MUX 33 memory logic matrix is read. The MY bit control the reading process. If MY is set to a logic zero the row reading sequence is 0-1-2.....33 (fig.12). If MY is set to a logic one the reading sequence is 32....1-33 (Fig 13).

The icon row (BANK8) is always the last being output either MY bit is a logic one or zero.

The functions related to bit TRS is the same as in MUX 65 mode.

In fig. 11 is shown the output drivers pad connection for MUX 33 mode. Note that the unused BANK 0-3 row drivers become columns drivers.

Using the STE2000 for driving a 33x128 graphic display matrix (or smaller) the user may only refer to bank 4 to 8, without taking into account the logic matrix re-mapping, built to enlarge the number of columns available. If a 33x128 LCD matrix is driven, the output row drivers R0-R15 and R32-R47 should be left floating. The correspondence between the Memory rows (bank 4-8) and the output drivers after reset is the one specified in fig. 11.

Figure 10. Physical 65x128 memory matrix and 33x160 correspondence

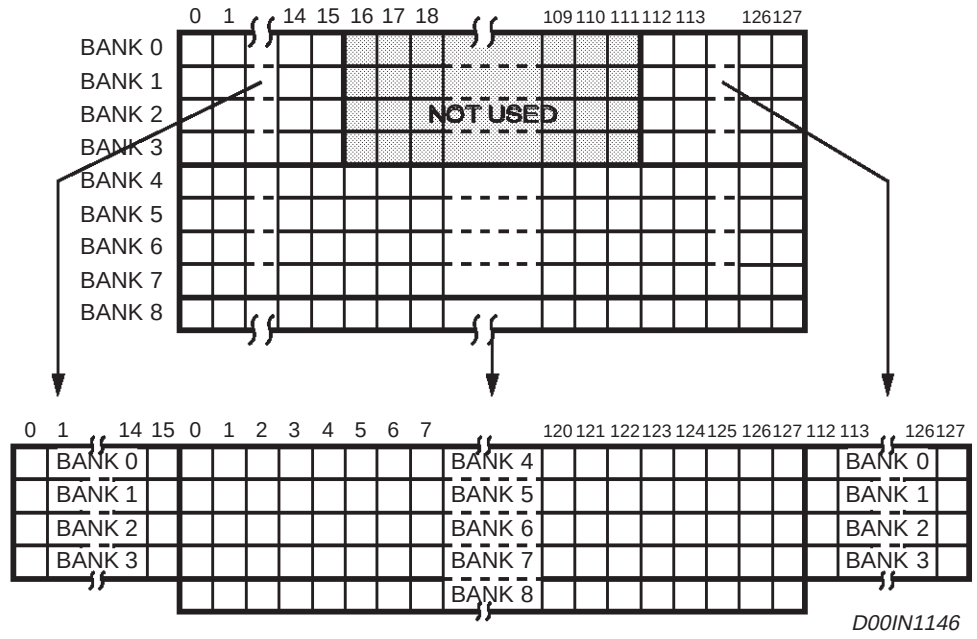


Figure 11. MUX 33 Output drivers connection

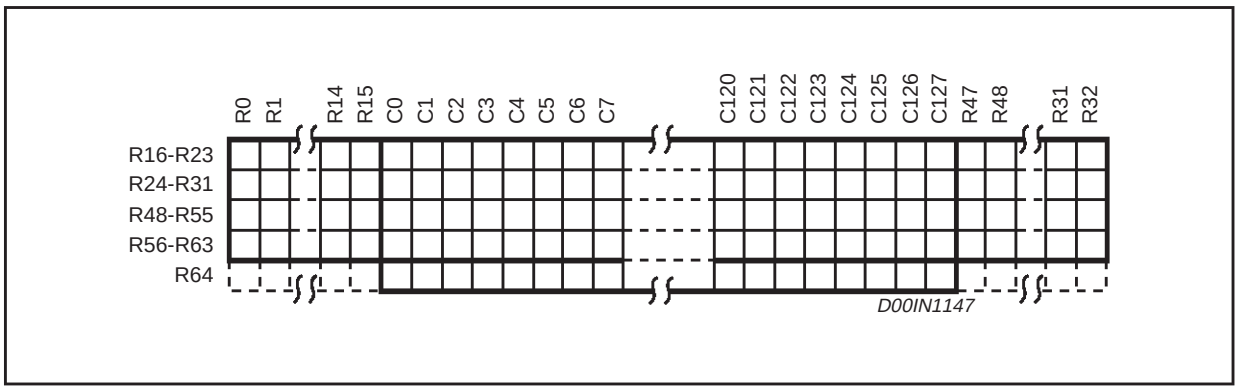


Figure 12. Output drivers rows and logical memory rows correspondence with MY = 0

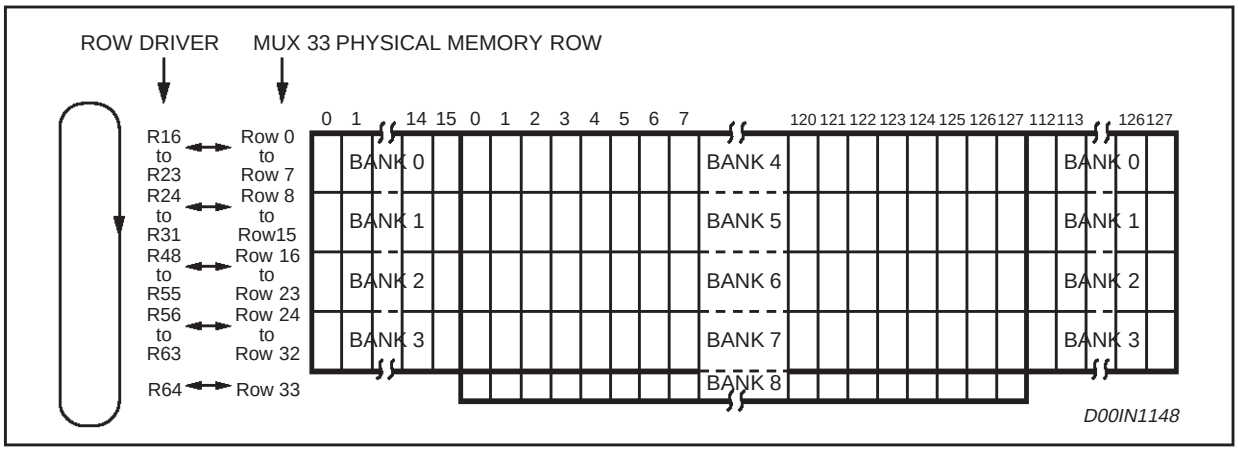
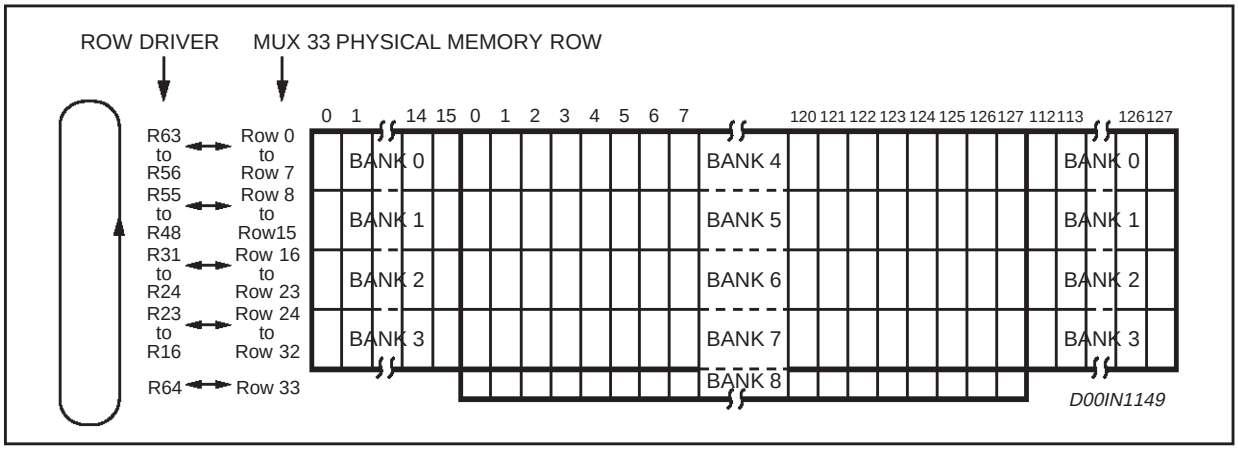


Figure 13. Output drivers rows and logical memory rows correspondence with MY = 1



Instruction Set

Two different instructions formats are provided:

- With D/$\overline{C}$ set to LOW

commands are sent to the Control circuitry.

- With D/$\overline{C}$ set to HIGH

the Data RAM is addressed Instructions have the syntax summarized in Table.1.

Reset (RES)

At power-on, all internal registers and RAM content are not defined. A Reset pulse must be applied on RES pad (active low) to initialize the internal registers content (see Tables 3,4,5,&6). Every on-going communication with the host controller is interrupted. The IC after the reset pulse is programmed in Power Down mode.

The Default configurations is:

- Horizontal addressing (V = 0)
- Normal instruction set (H = 0)
- Normal display (MX = MY = TRS =BRS = 0)
- MUX 65 mode (MUX = 0)
- Display blank (E = D = 0)
- Address counter X[6: 0] = 0 and Y[3 : 0] = 0
- Temperature coefficient (TC[1 : 0] = 0)
- Bias system (BS[2 : 0] = 0)
- V_{OP} = 0
- Power Down (PD = 1)

To clear the RAM content a MEMORY BLANK instruction should be executed.

Power Down (PD = 1)

When at Power Down, all LCD outputs are kept at V_{SS} (display off). Bias generator and V_{LCD} generator are OFF (V_{LCDOUT} output is discharged to V_{SS}, and then is possible to disconnect V_{LCDOUT}). The internal Oscillator is in off state. An external clock can be provided. The RAM contents is not cleared.

Charge Pump Factor

The desired Charge Pump Multiplication Factor can be programmed though the S1 and S0 bits, as follows:

S1	S0	Multiplication Factor
0	0	2X
0	1	3X
1	0	4X
1	1	5X

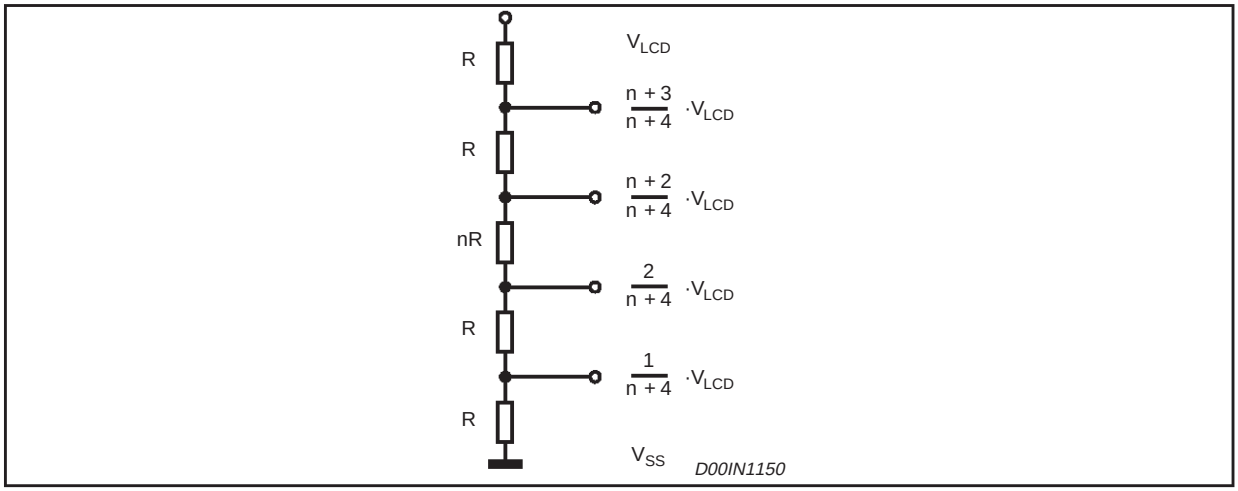
At Reset the X2 factor is selected.

Bias Levels

To properly drive the LCD, six (Including VLCD and VSS) different voltage (Bias) levels are generated. The ratios among these levels and VLCD, should be selected according to the MUX ratio (m). They are established to be (Fig. 14):

$$V_{LCD}, \frac{n+3}{n+4} V_{LCD}, \frac{n+2}{n+4} V_{LCD}, \frac{2}{n+4} V_{LCD}, \frac{1}{n+4} V_{LCD}, V_{SS}$$

Figure 14. Bias level Generator



thus providing an 1/(n+4) ratio, with n calculated from:

$$n = \sqrt{m} - 3$$

For m = 65, n = 5 and an 1/9 ratio is set.

For m = 33, n =3 and an 1/7 ratio is set.

The STE2000 provides three bits (BS0, BS1, BS2) for programming the desired Bias Ratio as shown below:

BS2	BS1	BS0	n
0	0	0	7
0	0	1	6
0	1	0	5
0	1	1	4
1	0	0	3
1	0	1	2
1	1	0	1
1	1	1	0

The following table Bias Level for m = 65 and m = 33 are provided:

Symbol	m = 65 (1/9)	m = 33 (1/7)
V1	V_{LCD}	V_{LCD}
V2	8/9*V_{LCD}	6/7* V_{LCD}
V3	7/9*V_{LCD}	5/7* V_{LCD}
V4	2/9*V V_{LCD}	2/7* V_{LCD}
V5	1/9 *V_{LCD}	1/7* V_{LCD}
V6	V_{SS}	V_{SS}

LCD Voltage Generation

The LCD Voltage at reference temperature (To = 27°C) can be set using the VOP register content according to the following formula:

$$V_{LCD}(T=To) = V_{LCD}o = (Ai+V_{OP} \cdot B) \qquad (i=0,1)$$

with the following values:

Symbol	Value	Unit	Note
Ao	2.94	V	PRS = 0
A1	6.75	V	PRS = 1
B	0.03	V	
To	27	°C	

Note that the two PRS value produces two adjacent ranges for VLCD. If the register and PRS bit are set to zero the internal voltage generator is switched off.

The proper value for the VLCD is a function of the Liquid Crystal Threshold Voltage (Vth) and of the Multiplexing Rate. A general expression for this is:

$$V_{LCD} = \frac{1+\sqrt{m}}{\sqrt{2 \cdot \left(1-\frac{1}{\sqrt{m}}\right)}} \cdot V_{th}$$

For MUX Rate m = 65 the ideal V_{LCD} is:

$$V_{LCD(to)} = 6.85 \cdot V_{th}$$

than:

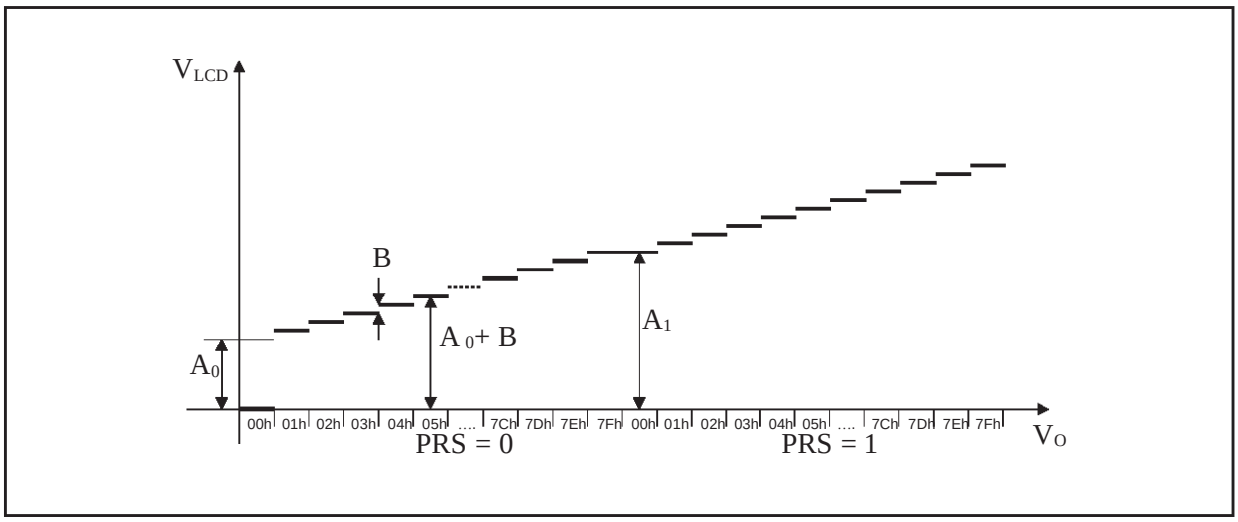
$$V_{op} = \frac{(6.85 \cdot V_{th} - A_i)}{0.03}$$

Temperature Coefficient

As the viscosity, and therefore the contrast, of the LCD are subject to change with temperature, there's the need to vary the LCD Voltage with temperature. The STE2000 provides the possibility to change the VLCD in a linear fashion against temperature with four different Temperature Coefficient selectable through the TC0 and TC1 bits.

TC1	TC0	Value	Unit
0	0	$-0.0X10^{-3}$	1/ °C
0	1	$-0.76X10^{-3}$	1/°C
1	0	$-1.05X10^{-3}$	1/°C
1	1	$-2.10X10^{-3}$	1/°C

Figure 15.



Finally, the V_{LCD} voltage at a given (T) temperature can be calculated as:

$$V_{LCD}(T) = V_{LCD}o \cdot [1 + (T\text{-}To) \cdot TC]$$

Memory Blanking Procedure

This instruction allows to fill the memory with "blank" patterns, in order to delete patterns randomly generated in memory when starting up the device. This instruction substitutes (128X9) single "write" instructions. It is possible to program "Memory Blanking Procedure" only under the following conditions:

- X address = 0
- Y address = 0
- V bit = 0
- PD bit = 0
- MX bit = 0

The end of the procedure will be notified on the $\overline{\text{BSY\_FLG}}$ pad going HIGH (while LOW the procedure is running). Any instruction programmed with $\overline{\text{BSY\_FLG}}$ LOW will be ignored that is, no instruction can be programmed for a period equivalent to 128X9 internal write cycles (128X9X1/fclock). The start of Memory blanking procedure will be between one and two fclock cycles from the last active edge (E rising edge for the parallel interface, last SCLK rising edge for the Serial interface, last SCL rising edge for the I^2C interface).

Checker Board Procedure

This instruction allows to fill the memory with "checker-board" pattern. It is mainly intended to developers, who can now simply obtain complex module test configuration by means of a single instruction. It is possible to program "Checker Board Procedure" only under the following conditions:

- X address = 0
- Y address = 0
- V bit = 0
- PD bit = 0
- MX bit = 0

The end of the procedure will be notified on the $\overline{BSY\_FLG}$ pad going HIGH, while LOW the procedure is running. Any instruction programmed with $\overline{BSY\_FLG}$ LOW will be ignored, that is, no instruction can be programmed for a period equivalent to 128X9 internal write cycles (128X9X1/fclock). The start of Memory blanking procedure will be between one and two fclock cycles from the last active edge (E rising edge for the parallel interface, last SCLK rising edge for the Serial interface, last SCL rising edge for the I^2C interface).

Scroll

The STE2000 can scroll the graphics display in units of raster-rows. The scrolling function is achieved changing the correspondence between the rows of the logical memory map and the output row drivers. The scroll function doesn't affect the data ram content. It is only related to the visualization process. The information output on the drivers is related to the row reading sequence (the 1st row read is output on R0, the 2nd on R1 and so on). Scrolling means reading the matrix starting from a row that is sequentially increased or decreased. After every scrolling command the offset between the memory address and the memory scanning pointer is increased or decreased by one. The offset range is between 0 to 63 in mux 65 mode and 0-31 in mux 33 mode. After the 64th scrolling command in mux 65 mode and after the 32th in mux 33 mode, the offset between the memory address and the memory scanning pointer is again zero (Cyclic Scrolling). Bank8 is always accessed last in each frame, and so isn't scrolled.

If the DIR Bit is set to a logic zero the offset register is increased by one and the raster is scrolled from top down. If the DIR Bit is set to a logic one the offset register is decreased by one and the raster is scrolled from bottom-up.

Bus Interfaces

To provide the widest flexibility and ease of use the STE2000 features three different methods for interfacing the host Controller. To select the desired interface the SEL1 and SEL2 pads need to be connected to a logic LOW (connect to GND) or a logic HIGH (connect to VDD). All the I/O pins of the unused interfaces must be connected to GND.

All interfaces are working while the STE2000 is in Power Down.

SEL2	SEL1	Interface	Note
0	0	I^2C	Read and Write; Fast and High Speed Mode
0	1	Serial	Write only
1	1	Parallel	Write only
1	0	Not Used	

I^2C Interface

The I^2C interface is a fully complying I^2C bus specification, selectable to work in both Fast (400kHz Clock) and High Speed Mode (3.4MHz).

This bus is intended for communication between different Ics. It consists of two lines: one bi-directional for data signals (SDA) and one for clock signals (SCL). Both the SDA and SCL lines must be connected to a positive supply voltage via an active or passive pull-up.

The following protocol has been defined:

- Data transfer may be initiated only when the bus is not busy.
- During data transfer, the data line must remain stable whenever the clock line is high. Changes in the data line while the clock line is high will be interpreted as control signals.

Accordingly, the following bus conditions have been defined:

BUS not busy: Both data and clock lines remain High.

Start Data Transfer: A change in the state of the data line, from High to Low, while the clock is High, define the START condition.

Stop Data Transfer: A Change in the state of the data line, from low to High, while the clock signal is High, defines the STOP condition.

Data Valid: The state of the data line represents valid data when after a start condition, the data line is stable for the duration of the High period of the clock signal. The data on the line may be changed during the Low period of the clock signal. There is one clock pulse per bit of data.

Each data transfer is initiated with a start condition and terminated with a stop condition. The number of data bytes transferred between the start and the stop conditions is not limited. The information is transmitted byte-wide and each receiver acknowledges with the ninth bit.

By definition, a device that gives out a message is called ”transmitter”, the receiving device that gets the signals is called ”receiver”. The device that controls the message is called ”master”. The devices that are controlled by the master are called ”slaves”

Acknowledge. Each byte of eight bits is followed by one acknowledge bit. This acknowledge bit is a low level put on the bus by the receiver, whereas the master generates an extra acknowledge related clock pulse.

A slave receiver which is addressed must generate an acknowledge after the reception of each byte. Also, a master receiver must generate an acknowledge after the reception of each byte that has been clocked out of the slave transmitter. The device that acknowledges has to pull down the SDA_IN line during the acknowledge clock pulse. Of course, setup and hold time must be taken into account. A master receiver must signal an end-of-data to the slave transmitter by not generating an acknowledge on the last byte that has been clocked out of the slave. In this case, the transmitter must leave the data line High to enable the master to generate the STOP condition.

Connecting SDA_IN and SDA_OUT together the SDA line become the standard data line. Having the acknowledge output (SDAOUT) separated from the serial data line is advantageous in Chip-On-Glass (COG) applications. In COG applications where the track resistance from the SDAOUT pad to the system SDA line can be significant, a potential divider is generated by the bus pull-up resistor and the Indium Tin Oxide (ITO) track resistance. It is possible that during the acknowledge cycle the STE2000 will not be able to create a valid logic 0 level. By splitting the SDA input from the output the device could be used in a mode that ignores the acknowledge bit. In COG applications where the acknowledge cycle is required, it is necessary to minimize the track resistance from the SDACK pad to the system SDA line to guarantee a valid LOW level.

To be compliant with the I^2C-bus Hs-mode specification the STE2000 is able to detect the special sequence ”S00001xxx”. After this sequence no acknowledge pulse is generated.

Since no internal modification are applied to work in Hs-mode, the device is able to work in Hs-mode without detecting the master code.

Figure 16. Bit transfer and START,STOP conditions definition

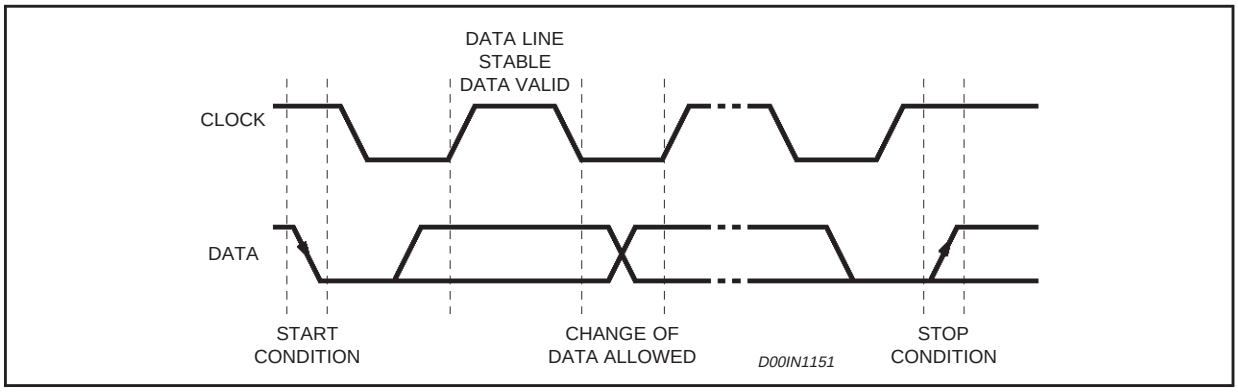


Figure 17. Acknowledgment on the I^2C-bus

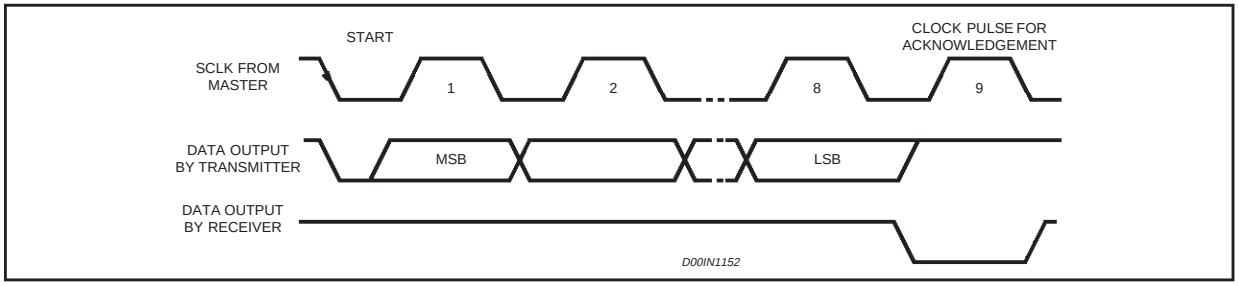
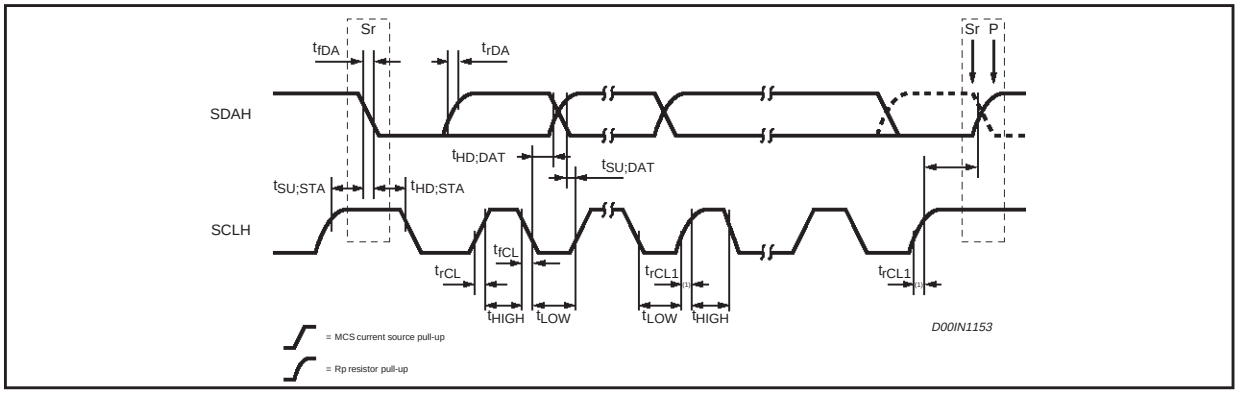


Figure 18. I^2C-bus timings



Communication Protocol

The STE2000 is an I^2C slave. The access to the device is bi-directional since data write and status read are allowed. Two are the device addresses available for the device. Both have in common the first 6 bits (011110). The least significant bit of the slave address is set by connecting the SA0 input to a logic 0 or to a logic 1.
To start the communication between the bus master and the slave LCD driver, the master must initiate a START condition. Following this, the master sends an 8-bit byte, shown in Fig. 18, on the SDA bus line (Most significant bit first). This consists of the 7-bit Device select Code, and the 1-bit Read/Write Designator (R/$\overline{W}$).
All slaves with the corresponding address acknowledge in parallel, all the others will ignore the I^2C-bus transfer.

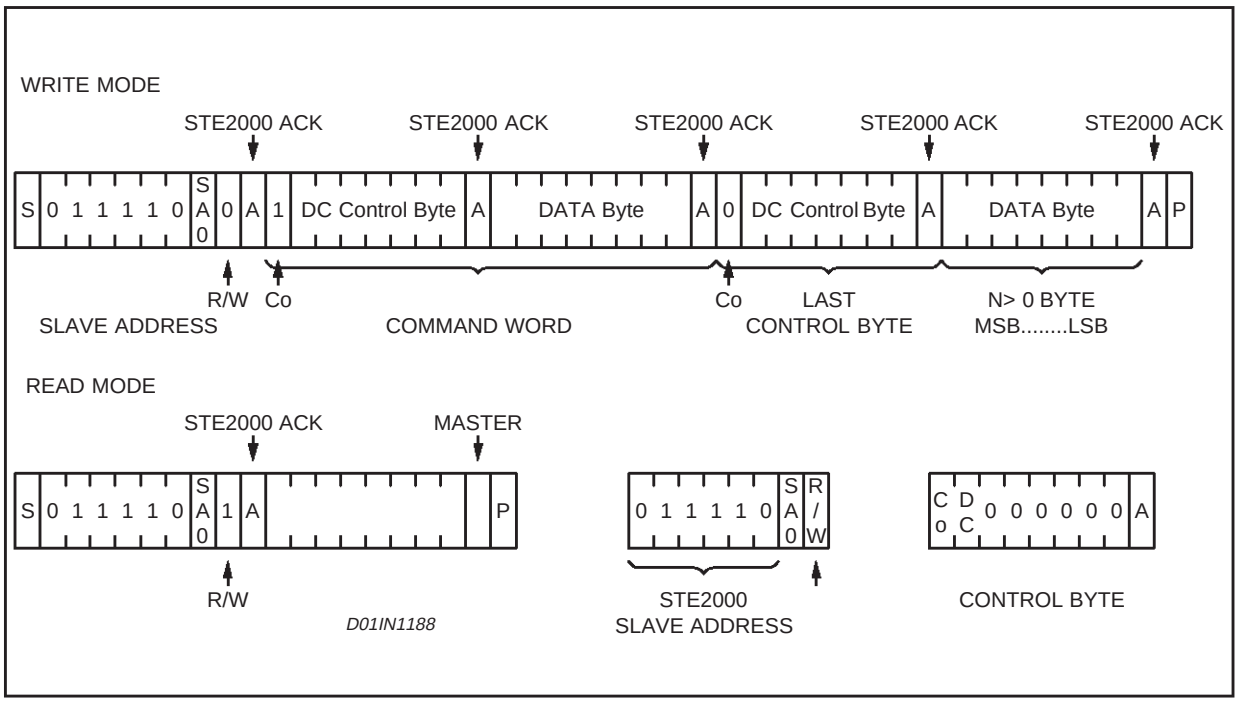
Writing Mode.

If the R/W bit is set to logic 0 the STE2000 is set to be a receiver. After the slaves acknowledge one or more command word follows to define the status of the device.
A command word is composed by two bytes. The first is a control byte which defines the Co and D/$\overline{C}$ values, the second is a data byte (fig 18). The Co bit is the command MSB and defines if after this command will follow one data byte and an other command word or if will follow a stream of data (Co = 1 Command word, Co = 0 Stream of data). The D/$\overline{C}$ bit defines whether the data byte is a command or RAM data (D/$\overline{C}$ = 1 RAM Data, D/$\overline{C}$ = 0 Command).
If Co =1 and D/$\overline{C}$ = 0 the incoming data byte is decoded as a command, and if Co =1 and D/$\overline{C}$ =1, the following data byte will be stored in the data RAM at the location specified by the data pointer.
very byte of a command word must be acknowledged by all addressed units.
After the last control byte, if D/$\overline{C}$ is set to a logic 1 the incoming data bytes are stored inside the STE2000 Display RAM starting at the address specified by the data pointer. The data pointer is automatically updated after every byte written and in the end points to the last RAM location written.
Every byte must be acknowledged by all addressed units.

Reading Mode.

If the R/W bit is set to logic 1 the chip will output data immediately after the slave address. If the D/C bit sent during the last write access, is set to a logic 0, the byte read is the status byte.

Figure 19. communication protocol



SERIAL INTERFACE

The STE2000 serial Interface is a unidirectional link between the display driver and the application supervisor.

It consists of four lines: one for data signals (SDIN), one for clock signals (SCLK), one for the peripheral enable ($\overline{SCE}$) and one for mode selection (SD/$\overline{C}$).

The serial interface is active only if the SCE line is set to a logic 0. When $\overline{SCE}$ line is high the serial peripheral power consumption is zero.

The STE2000 is always a slave on the bus and receive the communication clock on the SCLK pin from the master. The STE2000 is only able to receive data.

Information are exchanged byte-wide. During data transfer, the data line is sampled on the positive SCLK edge.

While $\overline{SCE}$ pin is high the serial interface is kept in reset.

SD/$\overline{C}$ line status indicates whether the byte is a command (SD/$\overline{C}$ =0) or RAM data (SD/$\overline{C}$ =1);it is read on the eighth SCLK clock pulse during every byte transfer.

If $\overline{SCE}$ stays low after the last bit of a command/data byte, the serial interface expects the MSB of the next byte at the next SCLK positive edge.

A reset pulse on $\overline{RES}$ pin interrupts the transmission. No data is written into the data RAM and all the internal registers are cleared.

If $\overline{SCE}$ is low after the positive edge of $\overline{RES}$, the serial interface is ready to receive data.

Figure 20. Serial bus protocol - one byte transmission

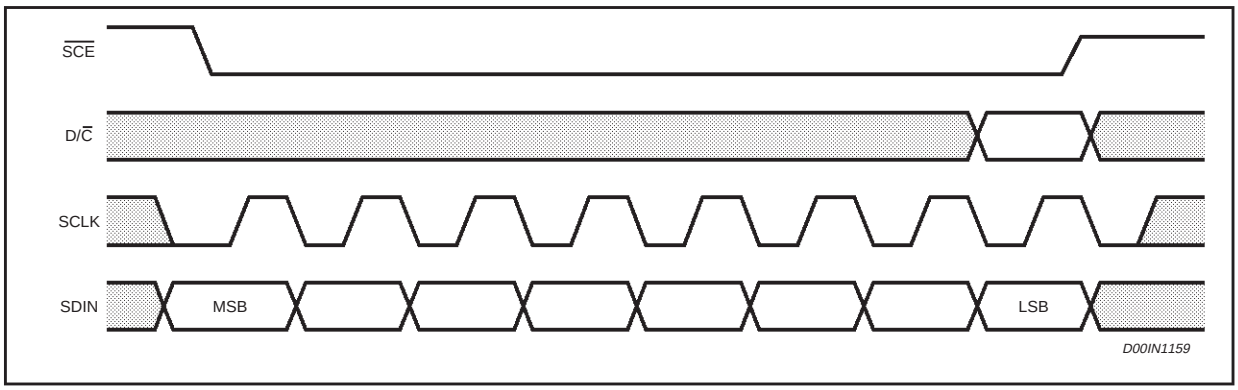


Figure 21. Serial bus protocol - several byte transmission

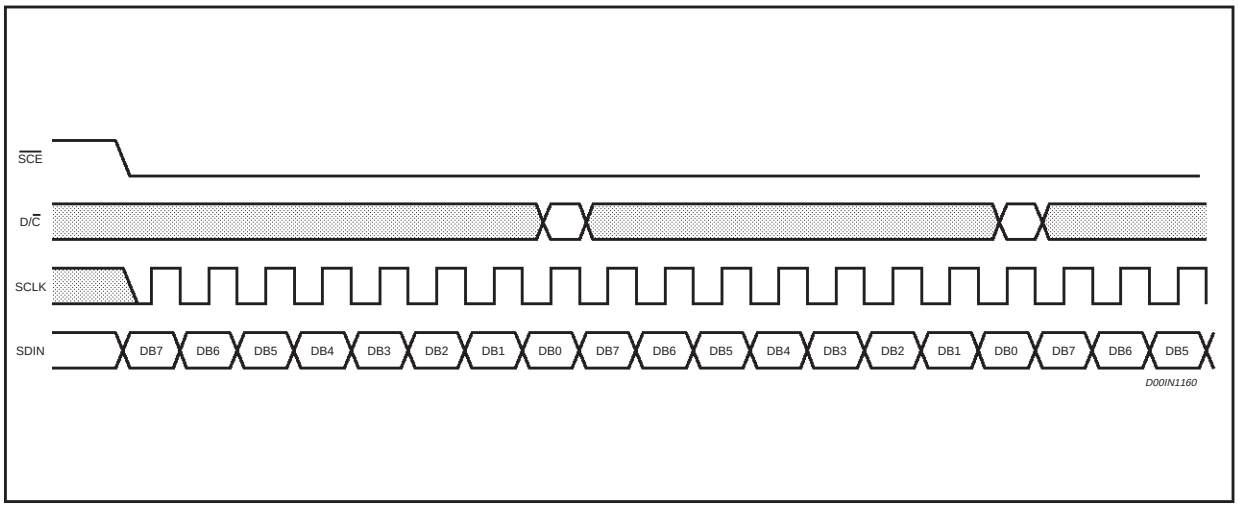
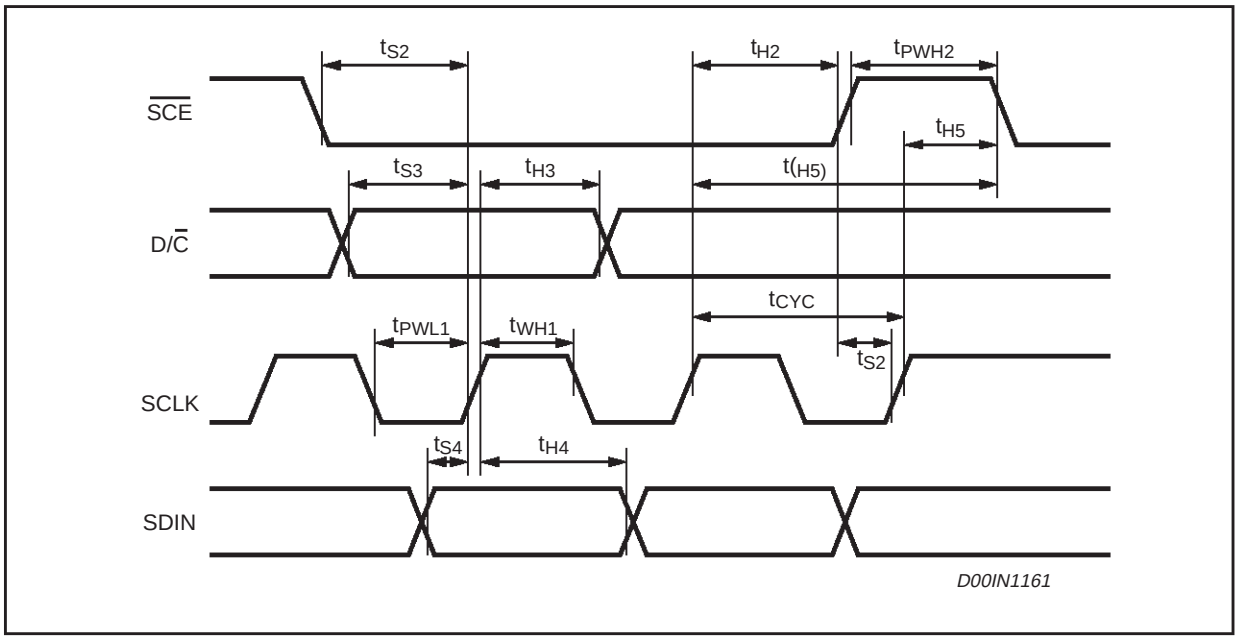


Figure 22. RESET effect on the serial interface



Parallel Interface

The STE2000 parallel Interface is a unidirectional link between the display driver and the application supervisor. It consists of ten lines: eight data lines (from DB7 to DB0) and two control lines. The control lines are: enable (E) for data latch and PD/$\overline{C}$ for mode selection.

The data lines and the control line values are internally latched on E rising edge (fig. 23).

Figure 23. Parallel interface timing

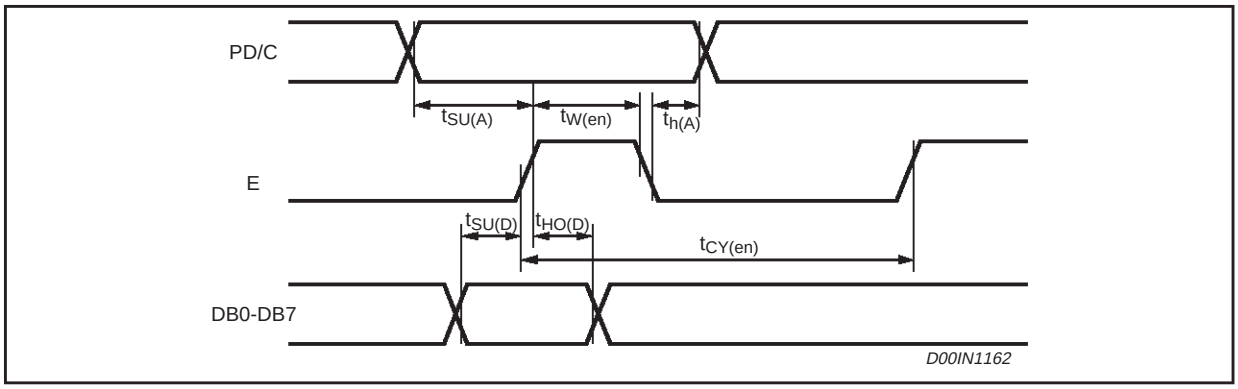


Table 1. Instruction Set

Instruction	D/C	R/W	B7	B6	B5	B4	B3	B2	B1	B0	Description
H=0 or H=1											
NOP	0	0	0	0	0	0	0	0	0	0	No Operation
Function Set	0	0	0	0	1	MX	MY	PD	V	H	Power Down Management; Entry Mode; Extended Instruction Set
Read Status Byte	0	1	PD	TRS	BRS	D	E	MX	MY	DO	(I^2C interface only)
Write Data	1	0	D7	D6	D5	D4	D3	D2	D1	D0	Writes data to RAM
H=0											
Memory Blank	0	0	0	0	0	0	0	0	0	1	Starts Memory Blank Procedure
Scroll	0	0	0	0	0	0	0	0	1	DIR	Scrolls by one Row UP or DOWN
V_{LCD} Range Setting	0	0	0	0	0	0	0	1	0	PRS	V_{LDC} programming range selection
Display Control	0	0	0	0	0	0	1	D	0	E	Select Display Configuration
Set CP Factor	0	0	0	0	0	1	0	0	S1	S0	Charge Pump Multiplication Factor
Set RAM Y	0	0	0	1	0	0	Y3	Y2	Y1	Y0	Set Horizontal (Y) RAM Address
Set RAM X	0	0	1	X6	X5	X4	X3	X2	X1	X0	Set Vertical (X) RAM Address
H=1											
Checker Board	0	0	0	0	0	0	0	0	0	1	Starts Checker Board Procedure
Multiplex Select	0	0	0	0	0	0	0	0	1	MUX	Selects MUX factor
TC Select	0	0	0	0	0	0	0	1	TC1	TC0	Set Temperature Coefficient for V_{LDC}
Output Address	0	0	0	0	0	0	1	DO	TRS	BRS	Set Row Order on Output Pads
Bias Ratios	0	0	0	0	0	1	0	BS2	BS1	BS0	Set desired Bias Ratios
Reserved	0	0	0	1	X	X	X	X	X	X	Not to be used
Set V_{OP}	0	0	1	OP6	OP5	OP4	OP3	OP2	OP1	OP0	V_{OP} register Write instruction

Table 2. Explanations of Table 6 symbols

BIT	0	1	RESET STATE
DIR	Scroll by one down	Scroll by one up	
H	Use basic instruction set	Use extended instruction set	0
PD	Device fully working	Device in power down	1
V	Horizontal addressing	Vertical addressing	0
MX	Normal X axis addressing	X axis address is mirrored.	0
MY	Image is displayed not vertically mirrored	Image is displayed vertically mirrored	0
TRS	No top rows mirroring	Top rows mirroring (row pads 16-31 & 48-64)	0
BRS	No bottom rows mirroring	Bottom rows mirroring (row pads 0-15 & 32-47)	0
DO	MSB on TOP	MSB on BOTTOM	0
PRS	V_{LCD} = 2.94V	V_{LCD} = 6.75V	0
MUX	1:65 multiplexing ratio	1:33 multiplexing ratio	0

Table 3.

D	E	DESCRIPTION	RESET STATE
0	0	display blank	
1	0	normal mode	D=0
0	1	all display segments on	E=0
1	1	inverse video mode	

Table 4.

S1	S0	DESCRIPTION	RESET STATE
0	0	Multiplication Factor 2X	
0	1	Multiplication Factor 3X	0
1	0	Multiplication Factor 4X	
1	1	Multiplication Factor 5X	

Table 5.

TC1	TC0	DESCRIPTION	RESET STATE
0	0	VLCD temperature Coefficient 0	
0	1	VLCD temperature Coefficient 1	00
1	0	VLCD temperature Coefficient 2	
1	1	VLCD temperature Coefficient 3	

Table 6.

BS2	BS1	BS0	DESCRIPTION	RESET STATE
0	0	0	Bias Ratio equal to 7	000
0	0	1	Bias Ratio equal to 6	
0	1	0	Bias Ratio equal to 5	
0	1	1	Bias Ratio equal to 4	
1	0	0	Bias Ratio equal to 3	
1	0	1	Bias Ratio equal to 2	
1	1	0	Bias Ratio equal to 1	
1	1	1	Bias Ratio equal to 0	

Figure 24. Application Schematic Using an External LCD Voltage Generator

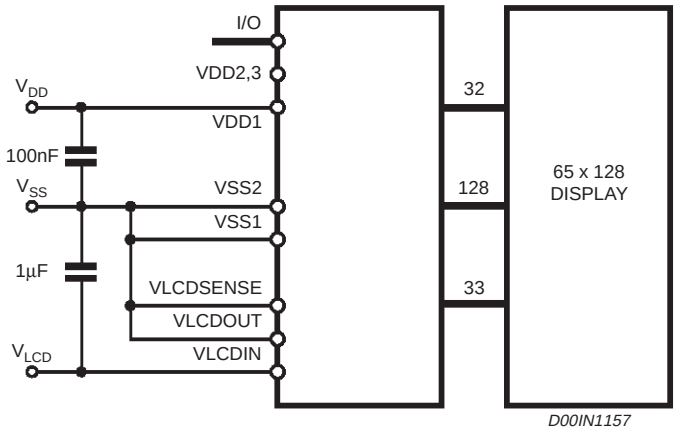


Figure 25. Application Schematic using the Internal LCD Voltage Generator and two separate supplies

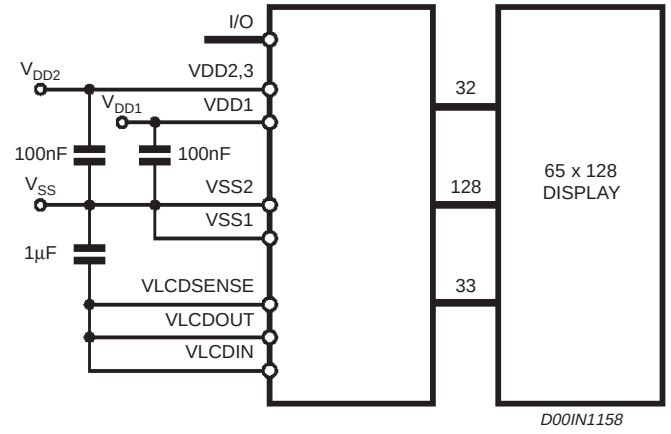


Figure 26. Application Schematic using the Internal LCD Voltage Generator and a single supply

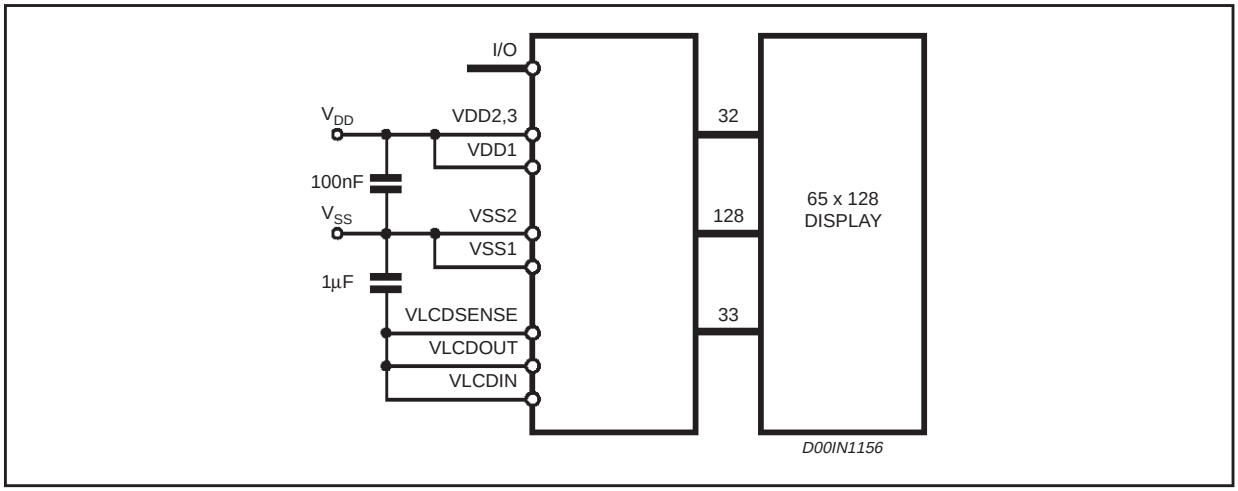


Figure 27. RESET timing diagram

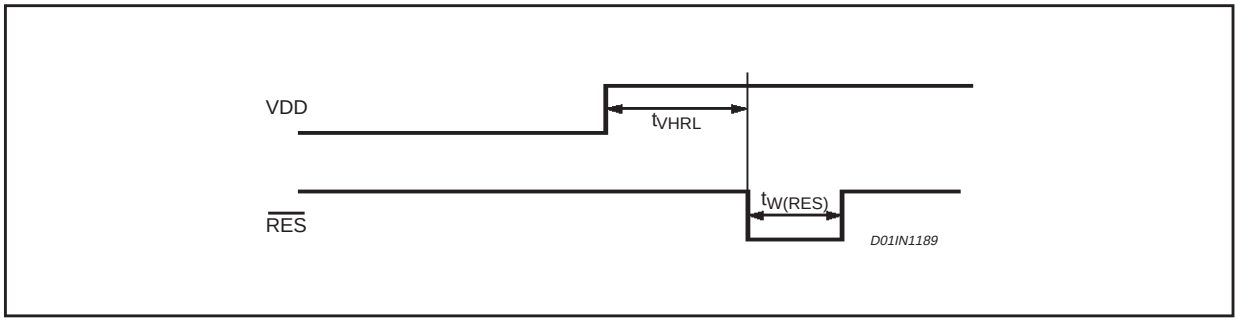


Figure 28. RESET timing diagram

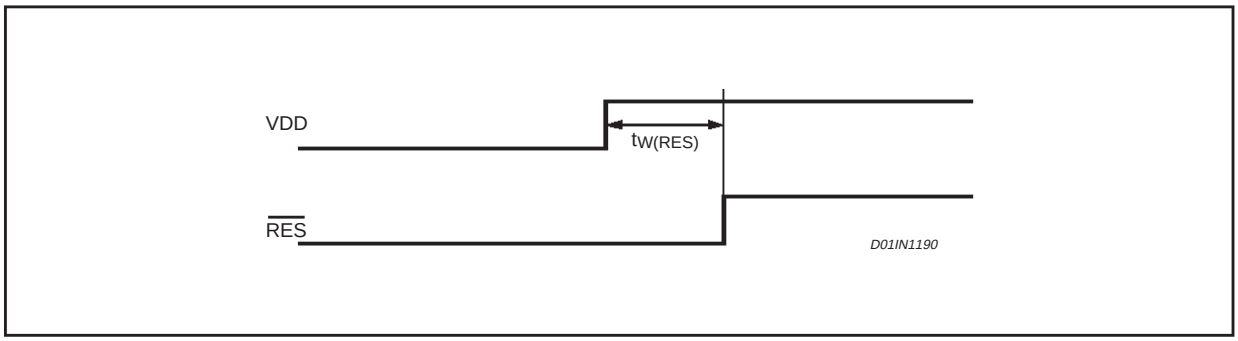


Figure 29. Chip Mechanical Drawing

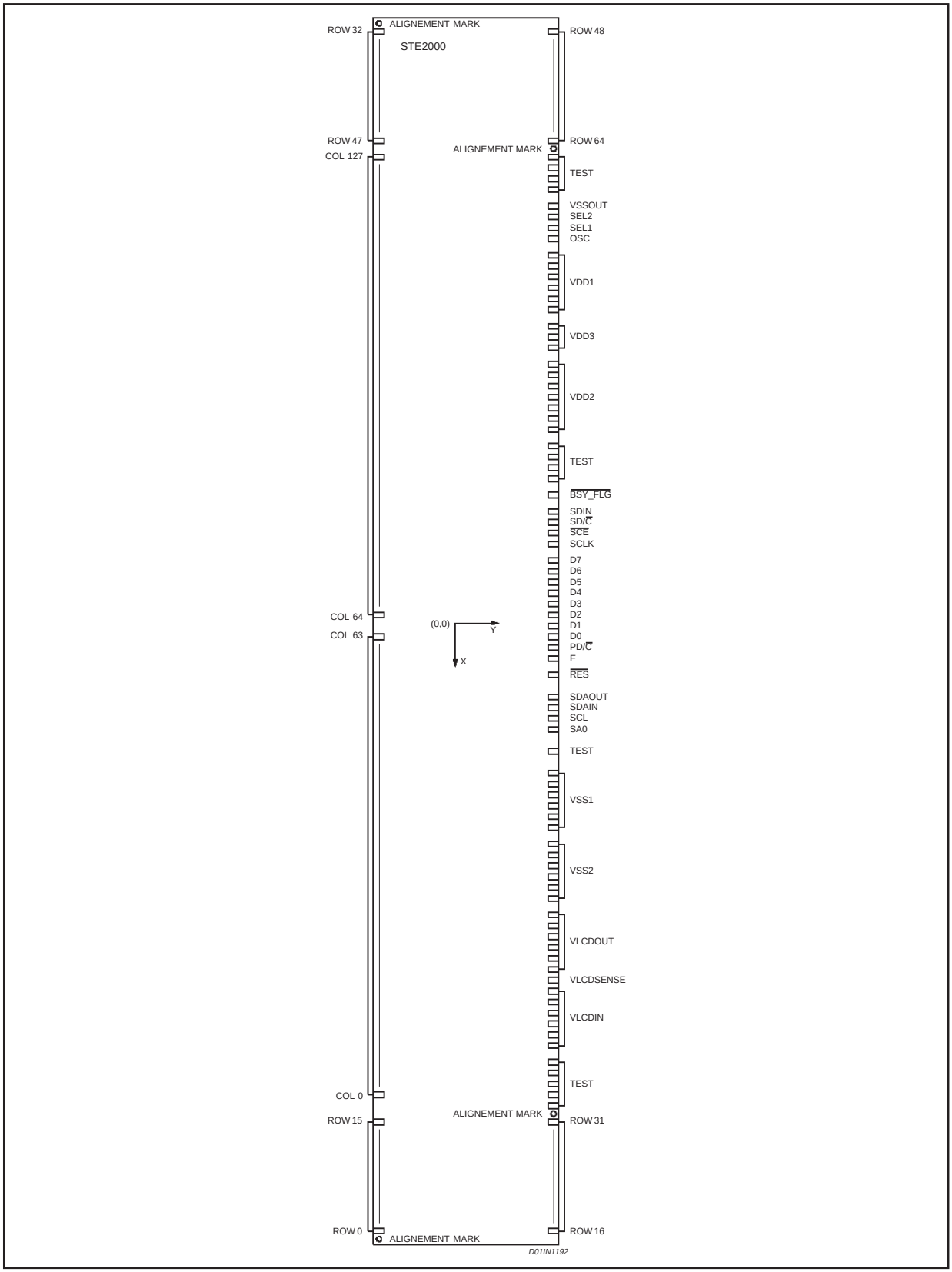


Figure 30. Improved ALTH & PLESKO Driving Method

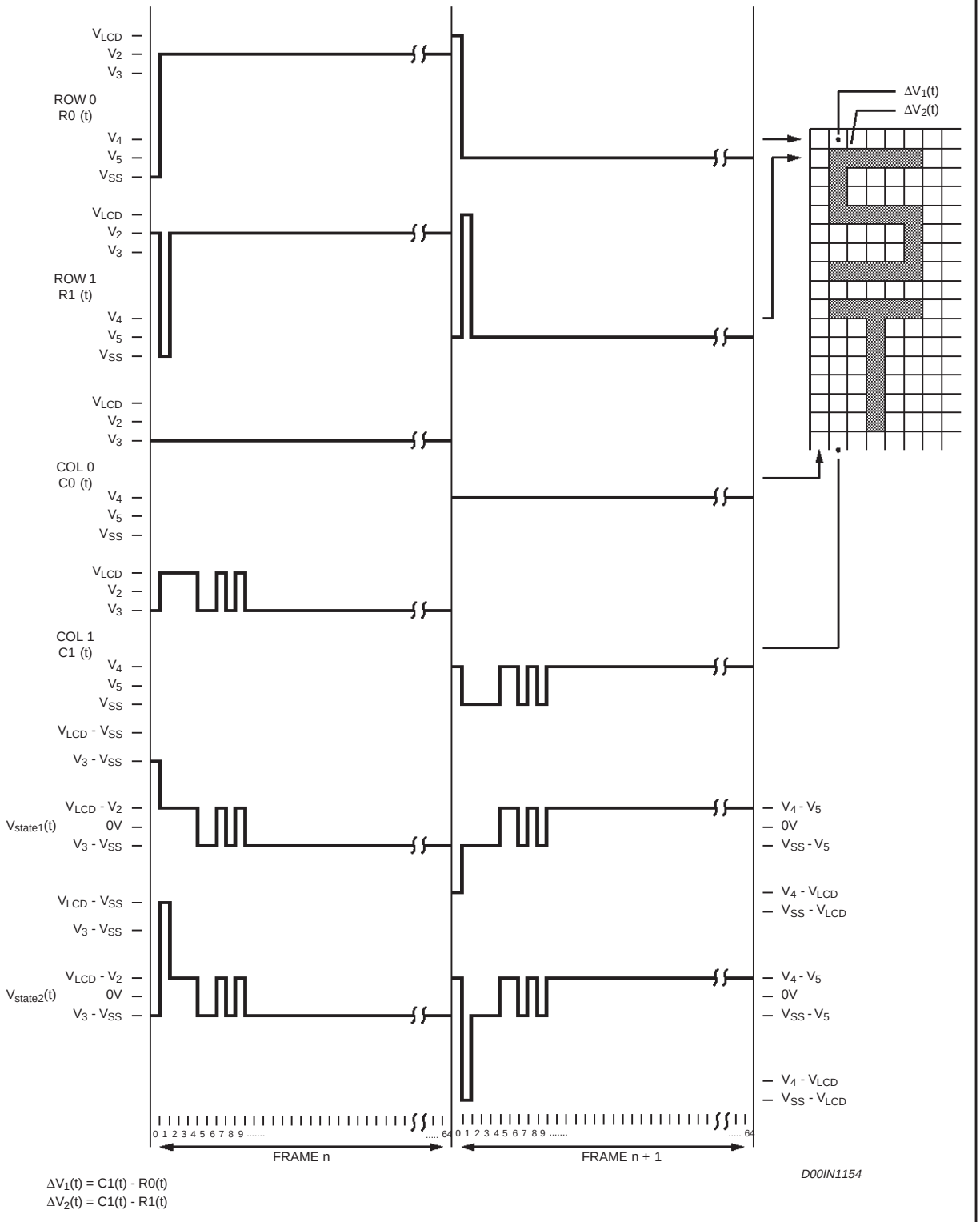


Figure 31. DATA RAM to display Mapping

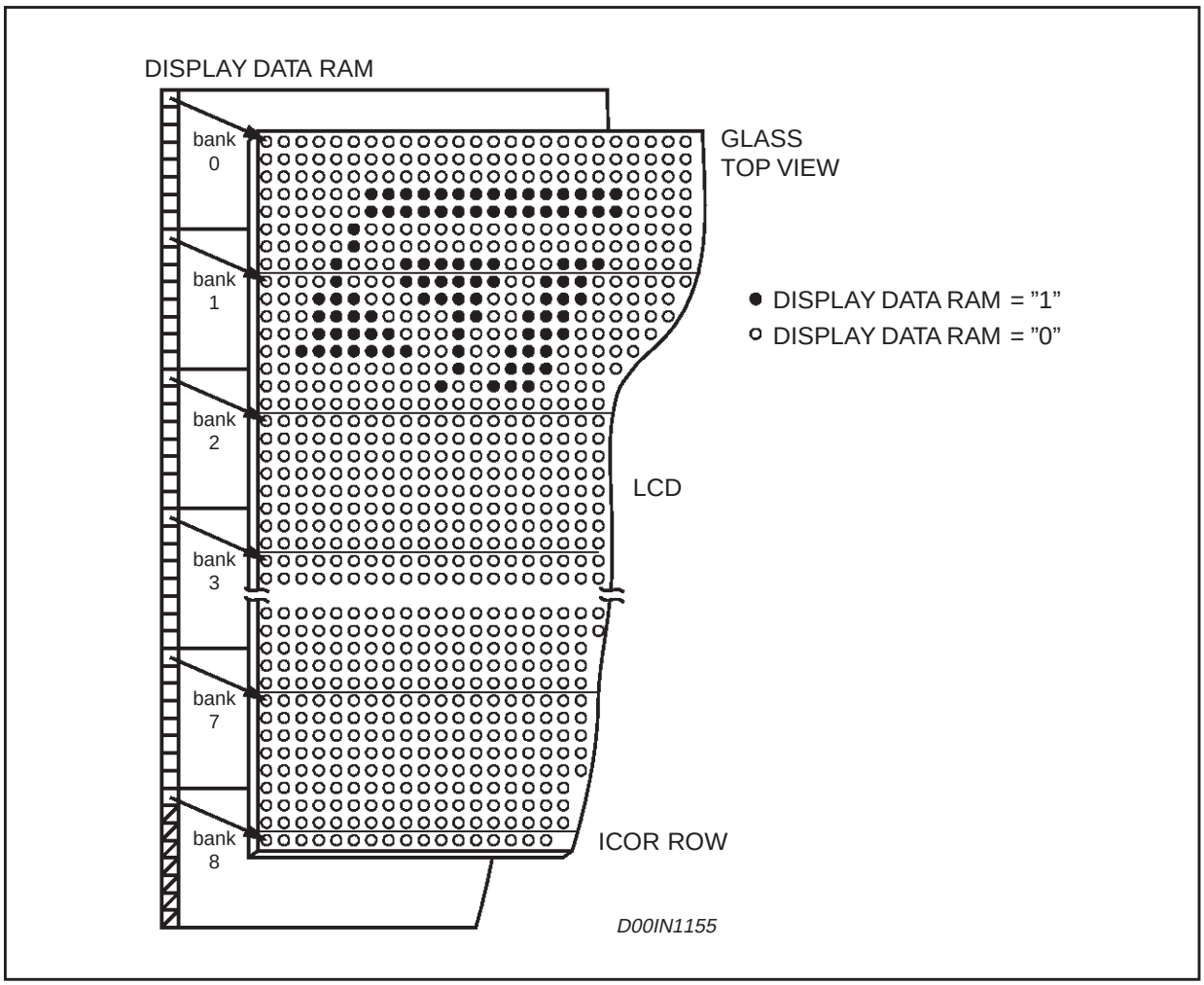


Table 7. Test Pin Configuration

Test Numb.	Pin
TEST_0 TEST_1 TEST_2 TEST_3	GND GND GND GND
TEST_4 TEST_5 TEST_6 TEST_7	OPEN OPEN OPEN OPEN
T8 T9	OPEN OPEN
TEST_10 TEST_11 TEST_12 TEST_13	OPEN OPEN OPEN OPEN

Table 8. Mechanical Dimensions

Die Size	2.12mmX12.5mm
Pad Pitch	70 µm
Pad Size	62um X 100 µm
Bump Dimensions	50µmX88µmX17.5
WFS Thickness	500µm

Table 9. Pad Coordinates

NAME	PAD	X (µm)	Y(µm)
R32	1	-5,993.84	-898.2
R33	2	-5,923.84	-898.2
R34	3	-5,853.84	-898.2
R35	4	-5,783.84	-898.2
R36	5	-5,713.84	-898.2
R37	6	-5,643.84	-898.2
R38	7	-5,573.84	-898.2
R39	8	-5,503.84	-898.2
R40	9	-5,433.84	-898.2
R41	10	-5,363.84	-898.2
R42	11	-5,293.84	-898.2
R43	12	-5,223.84	-898.2
R44	13	-5,153.84	-898.2
R45	14	-5,083.84	-898.2
R46	15	-5,013.84	-898.2
R47	16	-4,943.84	-898.2
C127	17	-4,585.44	-898.2
C126	18	-4,515.44	-898.2
C125	19	-4,445.44	-898.2
C124	20	-4,375.44	-898.2
C123	21	-4,305.44	-898.2
C122	22	-4,235.44	-898.2
C121	23	-4,165.44	-898.2
C120	24	-4,095.44	-898.2
C119	25	-4,025.44	-898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
C118	26	-3,955.44	-898.2
C117	27	-3,885.44	-898.2
C116	28	-3,815.44	-898.2
C115	29	-3,745.44	-898.2
C114	30	-3,675.44	-898.2
C113	31	-3,605.44	-898.2
C112	32	-3,535.44	-898.2
C111	33	-3,465.44	-898.2
C110	34	-3,395.44	-898.2
C109	35	-3,325.44	-898.2
C108	36	-3,255.44	-898.2
C107	37	-3,185.44	-898.2
C106	38	-3,115.44	-898.2
C105	39	-3,045.44	-898.2
C104	40	-2,975.44	-898.2
C103	41	-2,905.44	-898.2
C102	42	-2,835.44	-898.2
C101	43	-2,765.44	-898.2
C100	44	-2,695.44	-898.2
C99	45	-2,625.44	-898.2
C98	46	-2,555.44	-898.2
C97	47	-2,485.44	-898.2
C96	48	-2,415.44	-898.2
C95	49	-2,345.44	-898.2
C94	50	-2,275.44	-898.2
C93	51	-2,205.44	-898.2
C92	52	-2,135.44	-898.2
C91	53	-2,065.44	-898.2
C90	54	-1,995.44	-898.2
C89	55	-1,925.44	-898.2
C88	56	-1,855.44	-898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
C87	57	-1,785.44	-898.2
C86	58	-1,715.44	-898.2
C85	59	-1,645.44	-898.2
C84	60	-1,575.44	-898.2
C83	61	-1,505.44	-898.2
C82	62	-1,435.44	-898.2
C81	63	-1,365.44	-898.2
C80	64	-1,295.44	-898.2
C79	65	-1,225.44	-898.2
C78	66	-1,155.44	-898.2
C77	67	-1,085.44	-898.2
C76	68	-1,015.44	-898.2
C75	69	-945.44	-898.2
C74	70	-875.44	-898.2
C73	71	-805.44	-898.2
C72	72	-735.44	-898.2
C71	73	-665.44	-898.2
C70	74	-595.44	-898.2
C69	75	-525.44	-898.2
C68	76	-455.44	-898.2
C67	77	-385.44	-898.2
C66	78	-315.44	-898.2
C65	79	-245.44	-898.2
C64	80	-245.44	-898.2
C63	81	181.8	-898.2
C62	82	251.8	-898.2
C61	83	321.8	-898.2
C60	84	391.8	-898.2
C59	85	461.8	-898.2
C58	86	531.8	-898.2
C57	87	601.8	-898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
C56	88	671.8	-898.2
C55	89	741.8	-898.2
C54	90	811.8	-898.2
C53	91	881.8	-898.2
C52	92	951.8	-898.2
C51	93	1,021.8	-898.2
C50	94	1,091.8	-898.2
C49	95	1,161.8	-898.2
C48	96	1,231.8	-898.2
C47	97	1,301.8	-898.2
C46	98	1,371.8	-898.2
C45	99	1,441.8	-898.2
C44	100	1,511.8	-898.2
C43	101	1,581.8	-898.2
C42	102	1,651.8	-898.2
C41	103	1,721.8	-898.2
C40	104	1,791.8	-898.2
C39	105	1,861.8	-898.2
C38	106	1,931.8	-898.2
C37	107	2,001.8	-898.2
C36	108	2,071.8	-898.2
C35	109	2,141.8	-898.2
C34	110	2,211.8	-898.2
C33	111	2,281.8	-898.2
C32	112	2,351.8	-898.2
C31	113	2,421.8	-898.2
C30	114	2,491.8	-898.2
C29	115	2,561.8	-898.2
C28	116	2,631.8	-898.2
C27	117	2,701.8	-898.2
C26	118	2,771.8	-898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
C25	119	2,841.8	-898.2
C24	120	2,911.8	-898.2
C23	121	2,981.8	-898.2
C22	122	3,051.8	-898.2
C21	123	3,121.8	-898.2
C20	124	3,191.8	-898.2
C19	125	3,261.8	-898.2
C18	126	3,331.8	-898.2
C17	127	3,401.8	-898.2
C16	128	3,471.8	-898.2
C15	129	3,541.8	-898.2
C14	130	3,611.8	-898.2
C13	131	3,681.8	-898.2
C12	132	3,751.8	-898.2
C11	133	3,821.8	-898.2
C10	134	3,891.8	-898.2
C9	135	3,961.8	-898.2
C8	136	4,031.8	-898.2
C7	137	4,101.8	-898.2
C6	138	4,171.8	-898.2
C5	139	4,241.8	-898.2
C4	140	4,311.8	-898.2
C3	141	4,381.8	-898.2
C2	142	4,451.8	-898.2
C1	143	4,521.8	-898.2
C0	144	4,591.8	-898.2
R15	145	4,944	-898.2
R14	146	5,014	-898.2
R13	147	5,084	-898.2
R12	148	5,154	-898.2
R11	149	5,224	-898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
R10	150	5,294	-898.2
R9	151	5,364	-898.2
R8	152	5,434	-898.2
R7	153	5,504	-898.2
R6	154	5,574	-898.2
R5	155	5,644	-898.2
R4	156	5,714	-898.2
R3	157	5,784	-898.2
R2	158	5,854	-898.2
R1	159	5,924	-898.2
R0	160	5,994	-898.2
R16	161	6,021.92	898.2
R17	162	5,951.92	898.2
R18	163	5,881.92	898.2
R19	164	5,811.92	898.2
R20	165	5,741.92	898.2
R21	166	5,671.92	898.2
R22	167	5,601.92	898.2
R23	168	5,531.92	898.2
R24	169	5,461.92	898.2
R25	170	5,391.92	898.2
R26	171	5,321.92	898.2
R27	172	5,251.92	898.2
R28	173	5,181.92	898.2
R29	174	5,111.92	898.2
R30	175	5,041.92	898.2
R31	176	4,971.92	898.2
TEST_8	177	4,780.48	898.2
TEST_11	178	4,700.48	898.2
TEST_10	179	4,620.48	898.2
TEST_13	180	4,540.48	898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
TEST_12	181	4,460.48	898.2
VLCDIN_6	182	4,390.48	898.2
VLCDIN_5	183	4,320.48	898.2
VLCDIN_4	184	4,250.48	898.2
VLCDIN_3	185	4,180.48	898.2
VLCDIN_2	186	4,110.48	898.2
VLCDIN_1	187	4,040.48	898.2
VLCSENSE	188	3,968.08	898.2
VLCDOUT_6	189	3,895.64	898.2
VLCDOUT_5	190	3,825.64	898.2
VLCDOUT_4	191	3,755.64	898.2
VLCDOUT_3	192	3,685.64	898.2
VLCDOUT_2	193	3,615.64	898.2
VLCDOUT_1	194	3,545.64	898.2
VSS2_6	195	2,776.68	898.2
VSS2_5	196	2,706.68	898.2
VSS2_4	197	2,636.68	898.2
VSS2_3	198	2,496.28	898.2
VSS2_2	199	2,426.28	898.2
VSS2_1	200	2,356.28	898.2
VSS1_6	201	2,215.88	898.2
VSS1_5	202	2,145.88	898.2
VSS1_4	203	2,075.88	898.2
VSS1_3	204	1,935.48	898.2
VSS1_2	205	1,865.48	898.2
VSS1_1	206	1,795.48	898.2
TEST_9	207	1,722.04	898.2
SA0	208	1,183.92	898.2
SCL	209	1,044.08	898.2
SDA_IN	210	904.24	898.2
SDA_OUT	211	764.4	898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
$\overline{\text{RES}}$	212	624.56	898.2
E	213	484.72	898.2
PD/$\overline{\text{C}}$	214	344.88	898.2
D0	215	205.04	898.2
D1	216	65.2	898.2
D2	217	-74.64	898.2
D3	218	-214.48	898.2
D4	219	-354.32	898.2
D5	220	-494.16	898.2
D6	221	-634	898.2
D7	222	-773.84	898.2
SCLK	223	-913.68	898.2
$\overline{\text{SCE}}$	224	-1,053.52	898.2
SD/$\overline{\text{C}}$	225	-1,193.36	898.2
SDIN	226	-1,333.2	898.2
BUSY_FLAG	227	-1,474.48	898.2
TEST_4	228	-1,614.32	898.2
TEST_5	229	-1,754.16	898.2
TEST_6	230	-1,894	898.2
TEST_7	231	-2,033.84	898.2
VDD2_7	232	-2,574.68	898.2
VDD2_6	233	-2,644.68	898.2
VDD2_5	234	-2,714.68	898.2
VDD2_4	235	-2,784.68	898.2
VDD2_3	236	-2,924.68	898.2
VDD2_2	237	-2,924.68	898.2
VDD2_1	238	-2,994.68	898.2
VDD3_3	239	-3,083.08	898.2
VDD3_2	240	-3,153.08	898.2
VDD3_1	241	-3,223.08	898.2
VDD1_6	242	-3,311.48	898.2

Table 9. Pad Coordinates (continued)

NAME	PAD	X (µm)	Y(µm)
VDD1_5	243	-3,381.48	898.2
VDD1_4	244	-3,451.48	898.2
VDD1_3	245	-3,521.48	898.2
VDD1_2	246	-3,591.48	898.2
VDD1_1	247	-3,661.48	898.2
OSC	248	-3,731.48	898.2
SEL1	249	-3,871.32	898.2
SEL2	250	-4,011.16	898.2
VSSOUT	251	-4,151	898.2
TEST_0	252	-4,221	898.2
TEST_1	253	-4,360.84	898.2
TEST_2	254	-4,500.68	898.2
TEST_3	255	-4,640.52	898.2
R64	256	-4,901.92	898.2
R63	257	-4,971.92	898.2
R62	258	-5,041.92	898.2
R61	259	-5,111.92	898.2
R60	260	-5,181.92	898.2
R59	261	-5,251.92	898.2
R58	262	-5,321.92	898.2
R57	263	-5,391.92	898.2
R56	264	-5,461.92	898.2
R55	265	-5,531.92	898.2
R54	266	-5,601.92	898.2
R53	267	-5,671.92	898.2
R52	268	-5,741.92	898.2
R51	269	-5,811.92	898.2
R50	270	-5,881.92	898.2
R49	271	-5,951.92	898.2
R48	272	-6,021.92	898.2

Table 10. Alignement marks coordinates

X	Y	MARKS
-4806.2	901.8	mark1
4876.2	901.8	mark2
6092.6	-901.8	mark3
-6092.6	-901.8	mark4

Figure 32. Alignement marks dimensions